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(54) Title: DIVERGING X-RAY SOURCES USING LINEAR ACCUMULATION

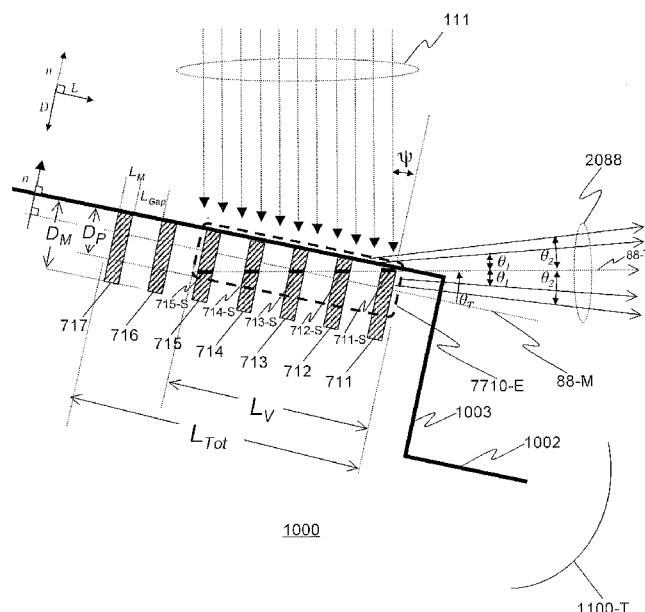


FIG. 19C

(57) Abstract: A compact source for high brightness x-ray generation is disclosed. The higher brightness is achieved through electron beam bombardment of multiple regions aligned with each other to achieve a linear accumulation of x-rays. This may be achieved through the use of x-ray targets that comprise microstructures of x-ray generating materials fabricated in close thermal contact with a substrate with high thermal conductivity. This allows heat to be more efficiently drawn out of the x-ray generating material, and allows bombardment of the x-ray generating material with higher electron density and/or higher energy electrons, leading to greater x-ray brightness. The orientation of the microstructures allows the use of a take-off angle at or near 0°, allowing the accumulation of x-rays from several microstructures to be aligned and be used to form a beam in the shape of an annular cone.

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DIVERGING X-RAY SOURCES USING LINEAR ACCUMULATION**CROSS-REFERENCE TO RELATED APPLICATIONS**

[0001] The Present Patent Application is a continuation-in-part of U.S. Patent Application No. 14/999,147, filed April 1, 2016 and entitled X-RAY SOURCES USING LINEAR ACCUMULATION, which claims the benefit of U.S. Provisional Patent Application No. 62/141,847, filed April 1, 2015 and entitled ADDITIONAL X-RAY SOURCE DESIGNS USING MICROSTRUCTURED TARGETS, and U.S. Provisional Patent Application No. 62/155,449, filed April 30, 2015, and entitled X-RAY TARGET FABRICATION, both of which are incorporated herein by reference in their entirety; and which in turn is also a continuation-in-part of U.S. Patent Application No. 14/490,672, filed Sept. 19, 2014 and entitled X-RAY SOURCES USING LINEAR ACCUMULATION, which claims the benefit of U.S. Provisional Patent Application Nos. 61/880,151, filed on Sep. 19, 2013, 61/894,073, filed on Oct. 22, 2013, 61/931,519, filed on Jan. 24, 2014, and 62/008,856, filed on Jun. 6, 2014, all of which are incorporated herein by reference in their entirety. This application claims priority to and claims the benefit of U.S.S.N. 15/166,274 filed May 27, 2016, which is incorporated herein by reference.

FIELD OF THE INVENTION

[0002] The embodiments of the invention disclosed herein relate to high-brightness sources of x-rays. Such high brightness sources may be useful for a variety of applications in which x-rays are employed, including manufacturing inspection, metrology, crystallography, spectroscopy, structure and composition analysis and medical imaging and diagnostic systems.

BACKGROUND OF THE INVENTION

[0003] X-ray sources have been used for over a century. One common x-ray source design is the reflection x-ray source 80, an example of which is illustrated in FIG. 1. The source comprises a vacuum environment (typically 10^{-6} torr or better) commonly maintained by a sealed vacuum tube 20 or active pumping, and is manufactured with sealed electrical leads 21 and 22 that pass from the negative and positive terminals of a high voltage source 10 outside the vacuum tube 20 to the various elements inside. The source 80 will typically comprise mounts 30 which secure the vacuum tube 20 in a housing 50, and the housing 50 may additionally comprise shielding material, such as lead, to prevent x-rays from being radiated by the source 80 in unwanted directions.

[0004] Inside the tube 20, an emitter 11 connected through the lead 21 to the high voltage source 10 serves as a cathode and generates a beam of electrons 111. A target 100 supported by a target substrate 110 is electrically connected to the opposite high voltage lead 22 and target support 32, and therefore serves as an anode. The electrons 111 accelerate towards the target 100 and collide with it at high energy, with the energy of the electrons determined by the magnitude of the accelerating voltage. The collision of the electrons 111 into the target 100 induces several effects, including the generation of x-rays 888, some of which exit the vacuum tube 20 through a window 40 or aperture.

[0005] In some prior art embodiments, the target 100 and substrate 110 may be integrated or comprise a solid block of the same material, such as copper (Cu). Electron optics (electrostatic or electromagnetic lenses) may also be provided to guide and shape the

path of the electrons, forming a more concentrated, focused beam at the target. Likewise, electron sources comprising multiple emitters may be provided to provide a larger, distributed source of electrons.

[0006] When the electrons collide with a target 100, they can interact in several ways. These are illustrated in FIG. 2. The electrons in the electron beam 111 collide with the target 100 at its surface 102, and the electrons that pass through the surface transfer their energy into the target 100 in an interaction volume 200, generally defined by the incident electron beam footprint (area) times the electron penetration depth.

[0007] An equation commonly used to estimate the penetration depth for electrons into a material is Potts' Law [P.J. Potts, Electron Probe Microanalysis, Ch. 10 of *A Handbook of Silicate Rock Analysis*, Springer Netherlands, 1987, p. 336)], which states that the penetration depth x in microns is related to the 10% of the value of the electron energy E_0 in keV raised to the $3/2$ power, divided by the density of the material:

$$x (\mu\text{m}) = 0.1 \times \frac{E_0^{1.5}}{\rho} \quad [\text{Eqn. 1}]$$

For less dense materials, such as a diamond substrate, the penetration depth is much larger than for a material with greater density, such as most elements used for x-ray generation.

[0008] There are several energy transfer mechanisms that can occur. Throughout the interaction volume 200, electron energy may simply be converted into heat. Some absorbed energy may excite the generation of secondary electrons, typically detected from a region 221 located near the surface, while some electrons may also be backscattered, which, due to their higher energy, can be detected from a somewhat larger region 231.

[0009] Throughout the interaction volume 200, including in the regions 221 and 231 near the surface and extending approximately 3 times deeper into the target 100, x-rays 888 are generated and radiated outward in all directions. A typical x-ray spectrum for radiation from the collision of 100 keV electrons with a tungsten target is illustrated in FIG. 3. The broad spectrum x-ray radiation 388, commonly called "bremsstrahlung", arises from electrons that were diverted from their initial trajectory. These continuum x-rays 388 are generated throughout the interaction volume, shown in FIG. 2 as the largest shaded portion 288 of the interaction volume 200. As was shown in FIG. 1, the x-ray source 80 will typically have a window 40, which may additionally comprise a filter, such as a sheet or layer of

aluminum, that attenuates the low energy x-rays, producing the modified energy spectrum 488 shown in FIG. 3. Characteristic x-rays, shown in FIG. 3 and indicated by 988, are primarily generated in a fraction of the electron penetration depth, shown as the second largest shaded portion 248 of the interaction volume 200. The relative depth is influenced in part by the energy of the electrons 111, which typically falls off with increasing depth. The actual dimensions of this interaction volume 200 may vary, depending on the energy and angle of incidence of the electrons, the surface topography and other properties (including local charge density), and the density and atomic composition of the target material.

[0010] Although x-rays may be radiated isotropically, as was illustrated in FIG. 2, only the x-ray radiation 888 within a small solid angle produced in the direction of a window in the source will be useful. X-ray brightness (also called “brilliance” by some), defined as the number of x-ray photons per second per solid angle in mrad^2 per area of the x-ray source in mm^2 , can be increased by adjusting the geometric factors to maximize the collected x-rays.

[0011] As illustrated in FIGs. 4A – 4C, the surface of a target 100 in a reflection x-ray source is generally mounted at an angle θ (as was also shown in FIG. 1). X-ray radiation through a window 440 is shown for a set of five equally spaced radiation spots 408 for three take-off angles: $\theta=60^\circ$ in FIG. 4A, $\theta=45^\circ$ in FIG. 4B, and $\theta=30^\circ$ in FIG. 4C. It can be seen that for lower take-off angles (e.g. FIG. 4C), the apparent spot size is reduced and thus apparent brightness increases.

[0012] In principle, it may appear that a take-off angle of $\theta=0^\circ$ would have the largest possible brightness. In practice, radiation at 0° occurs parallel to the surface of a solid metal target for conventional sources, and since the x-rays must propagate along a long length of the target material before emerging, most of the produced x-rays will be attenuated (reabsorbed) by the target material, reducing brightness. Thus a source with take-off angle of around 6° to 15° (depending on the source configuration, target material, and electron energy) is conventionally used.

[0013] Another way to increase the brightness of the x-ray source is to use a target material with a higher atomic number Z , as efficiency of x-ray production for bremsstrahlung radiation scales with increasingly higher Z . Furthermore, the x-ray radiating material should ideally have good thermal properties, such as a high melting point and high thermal conductivity, in order to allow higher electron power loading on the source to increase x-ray

production. Table I lists several materials that are commonly used for x-ray targets, several additional potential target materials (notably useful for specific characteristic lines of interest), and some materials that may be used as substrates for target materials. Melting points, and thermal and electrical conductivities are presented for values near 300°K (27°C). Most values are taken from the *CRC Handbook of Chemistry and Physics*, 90th ed. [CRC Press, Boca Raton, FL, 2009]. Other values are taken from various references.

Table I: Various Target and Substrate Materials and Selected Properties.

Material (Elemental Symbol)	Atomic Number Z	Melting Point °C (1 atm)	Thermal Conductivity (W/(m °C))	Electrical Conductivity (MS/m)
Common Target Materials:				
Chromium (Cr)	24	1907	93.7	7.9
Iron (Fe)	26	1538	80.2	10.0
Cobalt (Co)	27	1495	100	17.9
Copper (Cu)	29	1085	401	58.0
Molybdenum (Mo)	42	2623	138	18.1
Silver (Ag)	47	962	429	61.4
Tungsten (W)	74	3422	174	18.4
Potential Substrate Materials with low atomic number:				
Beryllium (Be)	4	1287	200	26.6
Carbon (C): Diamond	6	*	2300	10 ⁻¹⁹
Carbon (C): Graphite (in plane)	6	*	1950	0.25
Boron Nitride (BN)	B=5 N= 7	**	20	10 ⁻¹⁷
Silicon (Si)	14	1414	124	1.56 x 10 ⁻⁹
Silicon Carbide (β-SiC)	Si=14 C= 6	2798	0.49	10 ⁻⁹
Sapphire (Al ₂ O ₃) (C-axis)	Al=13 O= 8	2053	32.5	10 ⁻²⁰
*Carbon does not melt at 1 atm; it sublimes at ~3600 °C.				
**BN does not melt at 1 atm; it sublimes at ~2973 °C.				

[0014] Other ways to increase the brightness of the x-ray source are: increasing the electron current density, either by increasing the overall current or by focusing the electron beam to a smaller spot using, for example, electron optics; or by increasing the electron energy by increasing the accelerating voltage.

[0015] However, these improvements have a limit, in that all can increase the amount of heat generated in the interaction volume. If too much heat is generated within the target, damage can occur. One prior art technology developed to improve thermal management and mitigate this damage is the rotating anode system, illustrated in FIGs. 5A and 5B. In FIG. 5A, a cross-section is shown for a rotating anode x-ray source 580 comprising a target anode 500. The target anode 500 is connected by a shaft 530 to a rotor 520 supported by conducting bearings 524 that connect, through its mount 522, to the lead 22 and the positive terminal of the high voltage supply 10. The rotation of the rotor 520, shaft 530 and anode 500, all within the vacuum chamber 20, is typically driven inductively by stator windings 525 mounted outside the vacuum.

[0016] A top view of the target anode 500 is shown in more detail in FIG. 5B. The edge 510 of the rotating target anode 500 may be beveled at an angle, and the emitter 11 of the electron beam 511 directs the electron beam onto the beveled edge 510 of the target anode 500, generating x-rays 888 at an electron beam spot 501. As the electron beam spot 501 generates x-rays, the irradiated spot in the target heats up. However, as the target anode 500 rotates, the heated spot moves away from the beam spot 501, and the electron beam 511 now irradiates a cooler portion of the target anode 500. The hot spot has the time of one rotation to cool before becoming heated again when it again passes through the beam spot 501. By continuously rotating the target anode 500, x-rays appear to be generated from a fixed single spot, while the total area of the target illuminated by the electron beam is substantially larger than the electron beam spot, effectively spreading the electron energy deposition over a larger area (and volume).

[0017] Another approach to mitigating heat is to use a target with a thin layer of target x-ray generating material deposited onto a substrate with high heat conduction. Because the interaction volume is thin, for electrons with energies up to 100 keV the target material itself need not be thicker than a few microns, and can be deposited onto a substrate, such as diamond, sapphire or graphite that conducts the heat away quickly. [Diamond

mounted anodes for x-ray sources have been described by, for example, K. Upadhyaya et al. US Patent 4,972,449; B. Spitsyn et. al. US Patent 5,148,462; and M. Fryda et al., US Patent 6,850,598].

[0018] The substrate may also comprise channels for a coolant, that remove heat from the substrate [see, for example, Paul E. Larson, US Patent 5,602,899]. Water-cooled anodes are used for a variety of x-ray sources, including rotating anode x-ray sources.

[0019] The substrate may in turn be mounted to a heat sink comprising copper or some other material chosen for its thermally conducting properties. The heat sink may also comprise channels for a coolant [see, for example, Edward J. Morton, US Patent 8,094,784]. In some cases, thermoelectric coolers or cryogenic systems have been used to provide further cooling to an x-ray target mounted onto a heat sink.

[0020] Although these techniques to mitigate heat in x-ray sources have been developed, there are still limits on the ultimate x-ray brightness that may be achieved, particularly when the source is to be coupled to an x-ray optical system that collects x-rays only in a limited angular range. There is therefore a need for an x-ray source that may be used to achieve higher x-ray brightness through the use of a higher electron current density into a predefined angular range, and is still compact enough to fit in a laboratory or table-top environment.

BRIEF SUMMARY OF THE INVENTION

[0021] This disclosure presents x-ray sources that have the potential of being up to several orders of magnitude brighter than existing commercial x-ray technologies. The higher brightness is achieved in part through the use of novel configurations for x-ray targets used in generating x-rays from electron beam bombardment with specific design rules for the electron beam footprint and electron beam energy. The x-ray target configurations may comprise a number of microstructures of one or more selected x-ray generating materials fabricated in close thermal contact with (such as embedded in or buried in) a substrate with high thermal conductivity, such that the heat is more efficiently drawn out of the x-ray

generating material. This in turn allows bombardment of the x-ray generating material with higher electron power density, which leads to greater x-ray brightness.

[0022] A significant advantage to some embodiments is that the orientation of the microstructures allows the use of a take off angle at or near to zero degrees allowing the accumulation of x-rays from several microstructures for greater x-ray brightness.

[0023] Some embodiments of the invention comprise an additional cooling system to transport the heat away from the anode or anodes. Some embodiments of the invention additionally comprise rotating the anode or anodes comprising targets with microstructured patterns in order to further dissipate heat and increase the accumulated x-ray brightness.

BRIEF DESCRIPTION OF THE DRAWINGS

- [0024] FIG. 1 illustrates a schematic cross-section diagram of a standard prior art reflection x-ray source.
- [0025] FIG. 2 illustrates a cross-section diagram the interaction of electrons with a surface of a material in a prior art x-ray source.
- [0026] FIG. 3 illustrates the typical x-ray radiation spectrum for a tungsten target.
- [0027] FIG. 4A illustrates x-ray radiation from a prior art target for a target at a tilt angle of 60 degrees.
- [0028] FIG. 4B illustrates x-ray radiation from a prior art target for a target at a tilt angle of 45 degrees.
- [0029] FIG. 4C illustrates x-ray radiation from a prior art target for a target at a tilt angle of 30 degrees.
- [0030] FIG. 5A illustrates a schematic cross-section view of a prior art rotating anode x-ray source.
- [0031] FIG. 5B illustrates a top view of the anode for the rotating anode system of FIG. 5A.
- [0032] FIG. 6 illustrates a schematic cross-section view of an embodiment of an x-ray system according to the invention.

- [0033] FIG. 7 illustrates a perspective view of a target comprising a grid of embedded rectangular target microstructures on a larger substrate that may be used in some embodiments of the invention.
- [0034] FIG. 8 illustrates a cross-section view of electrons entering a target comprising target microstructures on a larger substrate that may be used in some embodiments of the invention.
- [0035] FIG. 9 illustrates a cross-section view of some of the x-rays radiated by the target of FIG. 8.
- [0036] FIG. 10 illustrates a perspective view of a target comprising a multiple rectangular microstructures arranged in a linear array on a substrate with a recessed region that may be used in some embodiments of the invention.
- [0037] FIG. 11A illustrates a perspective view of a target comprising a grid of embedded rectangular target microstructures that may be used in some embodiments of the invention.
- [0038] FIG. 11B illustrates a top view of the target of FIG. 11A.
- [0039] FIG. 11C illustrates a side/cross-section view of the target of FIGs. 11A and 11B.
- [0040] FIG. 12 illustrates a cross-section view of a portion of the target of FIGs. 11A – 11C, showing thermal transfer to a thermally conducting substrate under electron beam exposure.
- [0041] FIG. 13 illustrates a cross-section view of a target as shown in of FIG. 12 having an additional overcoat and a cooling channel.
- [0042] FIG. 14 illustrates a collection of x-ray emitters arranged in a linear array to produce linear accumulation as may be used in some embodiments of the invention.
- [0043] FIG. 15 illustrates a plot of the $1/e$ attenuation length for several materials for x-rays having energies ranging from 1 keV to 1,000 keV.
- [0044] FIG. 16 illustrates a schematic cross-section view of an embodiment of an x-ray system according to the invention comprising multiple electron emitters.
- [0045] FIG. 17A illustrates a schematic cross-section view of an embodiment of the invention comprising a ring pattern of x-ray generating structures on a rotating anode.

- [0046] FIG. 17B illustrates a schematic perspective view of the rotating anode of the embodiment of FIG. 17A.
- [0047] FIG. 17C illustrates a cross-section view of the rotating anode of the embodiment of FIG. 17A.
- [0048] FIG. 18 illustrates a schematic perspective view of a portion of an embodiment of the invention comprising a line pattern of x-ray generating structures on a rotating anode.
- [0049] FIG. 19A illustrates a cross-section view of the x-ray generating portion of a source according to an embodiment of the invention.
- [0050] FIG. 19B illustrates a perspective view of the x-ray generating portion of the source illustrated in FIG. 19A.
- [0051] FIG. 19C illustrates detailed cross-section view of the x-ray generating portion of the source illustrated in FIG. 19A.
- [0052] FIG. 20A illustrates a top-down view of the x-ray generating portion of a target used in the embodiment illustrated in FIGs. 19A – 19C.
- [0053] FIG. 20B illustrates an end view of the x-ray generating portion of a target used in the embodiment illustrated in FIGs. 19A – 19C.
- [0054] FIG. 20C illustrates a cross-section side view of the x-ray generating portion of a target used in the embodiment illustrated in FIGs. 19A – 19C.
- [0055] FIG. 21A illustrates a top-down view of the x-ray generating portion of a target having non-uniform x-ray generating structures.
- [0056] FIG. 21B illustrates an end view of the x-ray generating portion of the target of FIG. 21A.
- [0057] FIG. 21C illustrates a cross-section side view of the x-ray generating portion of the target of FIG. 21A.
- [0058] FIG. 22A illustrates a top-down view of the x-ray generating portion of the target used in the embodiment illustrated in FIGs. 19A – 19C under electron bombardment.
- [0059] FIG. 22B illustrates an end view of the x-ray generating portion of a target used in the embodiment illustrated in FIGs. 19A – 19C under electron bombardment.

- [0060] FIG. 22C illustrates a cross-section side view of the x-ray generating portion of a target used in the embodiment illustrated in FIGs. 19A – 19C under electron bombardment.
- [0061] FIG. 23 illustrates a cross-section side view of the x-ray generating portion of a target comprising a powder of x-ray generating material.
- [0062] FIG. 24A illustrates a top-down view of the x-ray generating portion of a target comprising structures of x-ray generating material arranged along the length dimension.
- [0063] FIG. 24B illustrates an end view of the x-ray generating portion of the target of FIG. 24A.
- [0064] FIG. 24C illustrates a cross-section side view of the x-ray generating portion of the target of FIG. 24A.
- [0065] FIG. 25 illustrates a cross-section view of the x-ray generating portion of a source according to the invention paired with an external x-ray optical element.
- [0066] FIG. 26 illustrates a cross-section view of a rotating anode according to the invention generating x-rays at a 0° take-off angle.
- [0067] FIG. 27 illustrates a cross-section view of a rotating anode according to the invention having a beveled surface and a non-zero take-off angle.
- [0068] Note: Elements shown in the drawings are meant to illustrate the functioning of embodiments of the invention, and have not necessarily been drawn in proportion or to scale.

DETAILED DESCRIPTIONS OF EMBODIMENTS OF THE INVENTION

1. A Basic Embodiment of the Invention.

[0069] FIG. 6 illustrates an embodiment of a reflective x-ray system 80-A according to the invention. As in the prior art reflective x-ray system 80 described above, the source comprises a vacuum environment (typically 10^{-6} torr or better) commonly maintained by a sealed vacuum chamber 20 or active pumping, and manufactured with sealed electrical leads 21 and 22. The source 80-A will typically comprise mounts 30, and the housing 50 may additionally comprise shielding material, such as lead, to prevent x-rays from being radiated by the source 80-A in unwanted directions.

[0070] Inside the chamber 20, an emitter 11 connected through the lead 21 to the negative terminal of a high voltage source 10 serves as a cathode and generates a beam of electrons 111. Any number of prior art techniques for electron beam generation may be used for the embodiments of the invention disclosed herein. Additional known techniques used for electron beam generation include heating for thermionic emission, Schottky emission (a combination of heating and field emission), or emitters comprising nanostructures such as carbon nanotubes). [For more on electron emission options for electron beam generation, see Shigehiko Yamamoto, "Fundamental physics of vacuum electron sources", Reports on Progress in Physics vol. 69, pp. 181–232 (2006)].

[0071] As before, a target 1100 comprising a target substrate 1000 and regions 700 of x-ray generating material is electrically connected to the opposite high voltage lead 22 and target support 32, thus serving as an anode. The electrons 111 accelerate towards the target 1100 and collide with it at high energy. The collision of the electrons 111 into the target 1100 induces several effects, including the generation of x-rays, some of which exit the vacuum tube 20 and are transmitted through at least one window 40 and/or an aperture 840 in a screen 84.

[0072] In some embodiments of the invention, there may also be an electron beam control mechanism 70 such as an electrostatic lens system or other system of electron optics that is controlled and coordinated with the electron dose and voltage provided by the emitter 11 by a controller 10-1 through a lead 27. The electron beam 111 may therefore be scanned, focused, de-focused, or otherwise directed onto the target 1100.

[0073] As illustrated in FIG. 6, the alignment of the microstructures 700 may be arranged such that the bombardment of several of the microstructures 700 by the electron beam or beams 111 will excite radiation in a direction orthogonal to the surface normal of the target such that the intensity in the direction of view will add or accumulate in that direction. The direction may also be selected by means of an aperture 840 in a screen 84 for the system to form the directional beam 888 that exits the system through a window 40. In some embodiments, the aperture 840 may be positioned outside the vacuum chamber, or, more commonly, the window 40 itself may serve as the aperture 840. In some embodiments, the aperture may be inside the vacuum chamber.

[0074] Targets such as those to be used in x-ray sources according to the invention disclosed herein have been described in detail in the co-pending US Patent Application entitled STRUCTURED TARGETS FOR X-RAY GENERATION (US Patent Application 14/465,816, filed Aug. 21, 2014), which is hereby incorporated by reference in its entirety, along with the provisional Applications to which this co-pending Application claims benefit. Any of the target designs and configurations disclosed in the above referenced co-pending Application may be considered for use as a component in any or all of the x-ray sources disclosed herein.

[0075] FIG. 7 illustrates a target 1100 as may be used in some embodiments of the invention. In this figure, a substrate 1000 has a region 1001 that contains an array of microstructures 700 comprising x-ray generating material (typically a metallic material) arranged in a regular array of right rectangular prisms. Electrons 111 bombard the target and generate x-rays in the microstructures 700. The material in the substrate 1000 is selected such that it has relatively low energy deposition rate for electrons in comparison to the x-ray generating microstructure material (typically by selecting a low Z material for the substrate). The material of the substrate 1000 may also be chosen to have a high thermal conductivity, typically larger than 100 W/(m °C). The microstructures are typically embedded within the substrate, i.e. if the microstructures are shaped as rectangular prisms, it is preferred that at least five of the six sides are in close thermal contact with the substrate 1000, so that heat generated in the microstructures 700 is effectively conducted away into the substrate 1000. However, targets used in other embodiments may have fewer direct contact surfaces. In general, when the term “embedded” is used in this disclosure, at least

half of the surface area of the microstructure will be in close thermal contact with the substrate.

[0076] A target 1100 according to the invention may be inserted as the target in a reflecting x-ray source geometry (e.g. FIG. 1), or adapted for use as the target used in the rotating anode x-ray source of FIGs. 5A and 5B.

[0077] It should be noted that the word “microstructure” in this Application will only be used for structures comprising materials selected for their x-ray generating properties. It should also be noted that, although the word “microstructure” is used, x-ray generating structures with dimensions smaller than the micrometer scale, or even as small as nano-scale dimensions (i.e. greater than 10 nm) may also be described by the word “microstructures” as used herein.

[0078] The microstructures may be placed in any number of relative positions throughout the substrate 1000. In some embodiments, as illustrated in FIG. 7, the target 1100 comprises a recessed shelf 1002. This allows the region 1001 comprising an array of microstructures 700 to be positioned flush with, or close to, a recessed edge 1003 of the substrate, and produce x-rays at or near zero angle without being reabsorbed by the substrate 1000, while providing a more symmetric heat sink for the heat generated when exposed to electrons 111. Some other embodiments may preferably have the microstructures placed near the edge of the substrate to minimize self-absorption.

[0079] FIG. 8 illustrates the relative interaction between a beam of electrons 111 and a target comprising a substrate 1000 and microstructures 700 of x-ray generating material. Three electron interaction volumes are illustrated, with two representing electrons bombarding the two shown microstructures 700, and one representing electrons interacting with the substrate.

[0080] As discussed in Eqn. 1 above, the depth of penetration can be estimated by Potts' Law. Using this formula, Table II illustrates some of the estimated penetration depths for some common x-ray target materials.

[0081] For the illustration in FIG. 8, if 60 keV electrons are used, and diamond ($Z=6$) is selected as the material for the substrate 1000 and copper ($Z=29$) is selected as the x-ray generating material for the microstructures 700, the dimension marked as R to the left side of FIG. 8 corresponds to a reference dimension of 10 microns, and the geometric depth

D_M of the x-ray generating material, which, when set to be 2/3 (66%) of the electron penetration depth for copper, becomes $D_M \approx 3.5 \mu\text{m}$.

Table II: Estimates of penetration depth for 60 keV electrons into some materials.

Material	Z	Density (g/cm ³)	Penetration Depth (μm)
Diamond	6	3.5	13.28
Copper	29	8.96	5.19
Molybdenum	42	10.28	4.52
Tungsten	74	19.25	2.41

[0082] The majority of characteristic Cu K x-rays are generated within depth D_M . The electron interactions below that depth are less efficient at generating characteristic Cu K-line x-rays but will contribute to heat generation. It is therefore preferable in some embodiments to set a maximum thickness for the microstructures in the target in order to optimize local thermal gradients. Some embodiments of the invention limit the depth of the microstructured x-ray generating material in the target to between one third and two thirds of the electron penetration depth of the x-ray generating material at the incident electron energy, while others may similarly limit based on the electron penetration depth with respect to the substrate material. For similar reasons, selecting the depth D_M to be less than the electron penetration depth is also generally preferred for efficient generation of bremsstrahlung radiation.

[0083] Note: Other choices for the dimensions of the x-ray generating material may also be used. In targets as used in some embodiments of the invention, the depth of the x-ray generating material may be selected to be 50% of the electron penetration depth of either the x-ray generating material or the substrate material. In other embodiments, the depth D_M for the microstructures may be selected related to the “continuous slowing down approximation” (CSDA) range for electrons in the material. Other depths may be specified depending on the x-ray spectrum desired and the properties of the selected x-ray generating material.

[0084] Note: In other targets as may be used in some embodiments of the invention, a particular ratio between the depth and the lateral dimensions (such as width W_M and length L_M) of the x-ray generating material may also be specified. For example, if the depth

is selected to be a particular dimension D_M , then the lateral dimensions W_M and/or L_M may be selected to be no more than $5 \times D_M$, giving a maximum ratio of 5. In other targets as may be used in some embodiments of the invention, the lateral dimensions W_M and/or L_M may be selected to be no more than $2 \times D_M$. It should also be noted that the depth D_M and lateral dimensions W_M and L_M (for width and length of the x-ray generating microstructure) may be defined relative to the axis of incident electrons, with respect to the x-ray emission path, and/or with respect to the orientation of the surface normal of the x-ray generating material. For electrons incident at an angle, care must be taken to make sure the appropriate projections for electron penetration depth at an angle are used.

[0085] FIG. 9 illustrates the relative x-ray generation from the various regions shown in FIG. 8. X-rays 888 comprising characteristic x-rays are generated from the region 248 where electron collisions overlap the microstructures 700 of x-ray generating material, while the regions 1280 and 1080 where the electrons interact with the substrate generate characteristic x-rays of the substrate element(s). Additionally, continuum bremsstrahlung radiation x-rays radiated from the region 248 of the microstructures 700 of the x-ray generating material may be stronger than the x-rays 1088 and 1288 produced in the regions 1280 and 1080.

[0086] It should be noted that, although the illustration of FIG. 9 shows x-rays radiated only to the right, this is in anticipation of a window or collector being placed to the right.

[0087] It should also be noted that materials are relatively transparent to their own characteristic x-rays, so that FIG. 9 illustrates an arrangement that allows the linear accumulation of characteristic x-rays along the microstructures, and therefore can be used to produce a relatively strong characteristic x-ray beam. However, lower energy x-rays may be attenuated by the target materials, which will effectively act as an x-ray filter. Other selections of materials and geometric parameters may be chosen (e.g. a non-linear scheme) if continuum x-rays are desired, (e.g. for near edge or extended fine structure spectroscopy).

[0088] Up to this point, targets that are arranged in planar configurations have been presented. These are generally easier to implement, since equipment and process recipes for deposition, etching and other planar processing steps are well known from processing

devices for microelectromechanical systems (MEMS) applications using planar diamond, and from processing silicon wafers for the semiconductor industry.

[0089] However, in some embodiments, a target with a surface with additional properties in three dimensions (3-D) may be desired. As discussed previously, when the electron beam is larger than the electron penetration depth, the apparent x-ray source size and area is at minimum (and brightness maximized) when viewed at a zero degree (0°) take-off angle.

[0090] The distance through which an x-ray beam will be reduced in intensity by $1/e$ is called the x-ray attenuation length, designated by μ_L , and therefore, a configuration in which the generated x-rays pass through as little additional material as possible, with the distance selected to be related to the x-ray attenuation length, may be desired.

[0091] An illustration of a portion of a target as may be used in some embodiments of the invention is presented in FIG. 10. In this target, an x-ray generating region 710 with seven microstructures 711, 712, 713, 714, 715, 716, 717 is configured near a recessed edge 1003 of the target substrate 1000 by a shelf 1002, similar to the situation illustrated in FIG. 7. As shown, the x-ray generating microstructures 711, 712, 713, 714, 715, 716, 717 are arranged in a linear array of x-ray generating right rectangular prisms embedded in the substrate 1000, and produce x-rays 1888 when bombarded with electrons 111.

[0092] The surface normal in the region of the microstructures 711 – 717 is designated by n , and the orthogonal length and width dimensions are defined to be in the plane perpendicular to the normal of said predetermined surface, while the depth dimension into the target is defined as parallel to the surface normal. The thickness D_M of the microstructures 711 – 717 in the depth direction is selected to be between one third and two thirds of the electron penetration depth of the x-ray generating material at the incident electron energy for optimal thermal performance. The width W_M of the microstructures 711 – 717 is selected to obtain a desired source size in the corresponding direction. As illustrated, $W_M \approx D_M$. As discussed previously, W_M could also be substantially smaller or larger, depending on the shape and size of the source spot desired.

[0093] As illustrated, the length of each of the microstructures 711 – 717 is $L_M \approx W_M/10$, and the length of the separation between each pair of microstructures is a distance $L_{Gap} \approx 2 L_M$, making the total length of the region 710 comprising x-ray generating

material $L_{Tot} = 7 \times L_M + 6 \times L_{Gap} \approx 19 \times L_M \approx 1.9 \times D_M$. In other embodiments, larger or smaller dimensions may also be used, depending on the amount of x-rays absorbed by the substrate and the relative thermal gradients that may be achieved between the specific materials of the x-ray generating microstructures 711 – 717 and the substrate 1000.

[0094] Likewise, the distance between the edge of the shelf and the edge of the x-ray generating material p as illustrated is $p \approx L_M$, but may be selected to be any value, from flush with the edge 1003 ($p=0$) to as much as 1 mm, depending on the x-ray reabsorption properties of the substrate material, the relative thermal properties, and the amount of heat expected to be generated when bombarded with electrons.

[0095] For a configuration such as shown in FIG. 10, the total length L_{Tot} of the x-ray generating region 710 will commonly be about twice the linear attenuation length μ_L for x-rays in the x-ray generating material, but can be selected to be half to more than 4 times that distance.

[0096] The microstructures may be embedded in the substrate (as shown), but in some embodiments they may also be partially embedded, or in other embodiments placed on top of the substrate.

[0097] The thermal benefits of a structured target such as that illustrated in FIG. 10 are presented in the U.S. Provisional Application 62/155,449, to which a parent Application of this Application claims the benefit of priority, and which has been incorporated by reference in this Application in its entirety.

[0098] In the cited Provisional Patent Application, calculations therein for two targets are presented using the finite element modeling product Solidworks Simulation Professional.

[0099] The first target modeled has a uniform coating of copper 300 microns thick as the x-ray material, as is common in commercial x-ray targets. Simulation of bombardment of the copper layer with electrons over an ellipse 10 microns wide and 66 microns long predicts an increase in the temperature of the copper to over 700 °C.

[0100] The second target, according to an embodiment of the invention, has 22 discrete structures of copper as the x-ray generating material, arranged in a one-dimensional array similar to that illustrated in FIG. 10. The microstructures of copper are embedded in diamond, and have an axis of orientation perpendicular to the surface normal of the target.

[0101] The length of each x-ray generating structure along the axis of the array L_M is 1 micron, and elements are placed with a separation L_{Gap} of 2 microns. The width of the elements in the direction perpendicular to the array axis W_M is 10 microns, and depth perpendicular from the surface into the target D_M is also 10 microns.

[0102] In the simulation, both targets are modeled as being bombarded with an electron beam that raises the temperature to the operating temperature of ~ 700 °C. The uniform copper target reaches this temperature with an electron exposure of 16 Watts. However, in the case of the second, structured target, the copper reaches the operating temperature of ~ 700 °C with an exposure of 65 Watts – a level 4 times higher. Normalizing for the reduced copper volume still gives more than twice the power deposited into the copper regions. Moreover, electron energy deposition rates between the materials is much more substantial in the higher density Cu than in diamond, and is therefore predicted to generate at least twice the number of x-rays. This demonstrates the utility of embedding microstructures of x-ray generating material into a thermally conducting substrate, in spite of a reduction in the total amount of x-ray generating material.

[0103] FIGs. 11A – 11C illustrate a region 1001 of a target as may be used in some embodiments of the invention that comprises an array of microstructures 700 in the form of right rectangular prisms comprising x-ray generating material arranged in a two-dimensional regular array. FIG. 11A presents a perspective view of the sixteen microstructures 700 for this target, while FIG. 11B illustrates a top down view of the same region, and FIG. 11C presents a side/cross-section view of the same region.

[0104] For a structure comprising the microstructures embedded in the substrate with a side/cross-section view as shown in FIG. 11C with depth D_M and lateral dimensions in the plane of the substrate of W_M and L_M , the ratio of the total surface area in contact with the substrate for the embedded microstructures vs. deposited microstructures is

$$\frac{A_{Embedded}}{A_{Deposited}} = 1 + 2D_M \frac{(W_M + L_M)}{(W_M \times L_M)} \quad [\text{Eqn. 2}]$$

With a small value for D_M relative to W_M and L_M , the ratio is essentially 1. For larger thicknesses, the ratio becomes larger, and for a cube ($D_M = W_M = L_M$) in which 5 equal sides are in thermal contact, the ratio is 5. If an overcoat or cap layer of a material with similar

properties as the substrate in terms of mass density and thermal conductivity is used, the ratio may be increased to 6.

[0105] The heat transfer is illustrated with representative arrows in FIG. 12, in which the heat generated in microstructures 700 embedded in a substrate 1000 is conducted out of the microstructures 700 through the bottom and sides (arrows for transfer through the sides out of the plane of the drawing are not shown). The amount of heat transferred per unit time conducted through a material of area A and thickness d increases with the temperature gradient, the thermal conductivity in $\text{W}/(\text{m } ^\circ\text{C})$, and the surface area through which heat is transferred. Embedding the microstructures in a substrate of high thermal conductivity increases all these factors.

[0106] FIG. 13 illustrates an alternative embodiment in which an overcoat has been added to the surface of the target. This overcoat 725 may be an electrically conducting layer, providing a return path to ground for the electrons bombarding the target. For such embodiments, the thin layer of conducting material that is preferably of relatively low atomic number, such as Titanium (Ti) is used. Other conducting materials, such as silver (Ag), copper (Cu), gold (Au), tungsten (W), aluminum (Al), beryllium (Be), carbon (C), graphene, or chromium (Cr) may be used to allow electrical conduction from the discrete microstructures 700 to an electrical path 722 that connects to a positive terminal relative to the high voltage supply. Such overcoats are typically thin films, with thickness on the order of 5 to 50 nm.

[0107] In other embodiments, this overcoat 725 may comprise a material selected for its thermal conductivity. In some embodiments, this overcoat 725 may be a layer of diamond, deposited by chemical vapor deposition (CVD). This allows heat to be conducted away from all sides of the microstructure. It may also provide a protective layer, preventing x-ray generating material from subliming away from the target during extended or prolonged use. Such protective overcoats typically have thicknesses on the order of 0.2 to 5 microns. Such a protective overcoat may also be deposited using an additional dopant to provide electrical conductivity as well. In some embodiments, two distinct layers, one to provide electrical conductivity, the other to provide thermal conductivity and/or encapsulation, may be used. In some embodiments, overcoats may comprise beryllium, diamond, polycrystalline

diamond, CVD diamond, diamond-like carbon, graphite, silicon, boron nitride, silicon carbide and sapphire.

[0108] In other embodiments the substrate may additionally comprise a cooling channel 1200, as also illustrated in FIG. 13. Such cooling channels may be a prior art cooling channel using flowing water or some other cooling fluid to conduct heat away from the substrate, or may be fabricated according to a design adapted to best remove heat from the regions near the embedded microstructures 700.

[0109] Other configurations that may be used in embodiments of the invention, such as a checkerboard array of microstructures, a non-planar “staircase” substrate and various non-uniform shapes of x-ray generating elements, have been described in the above cited parent Applications of the present Application, U.S. Patent Applications Ser. Nos. 14/490,672 and 14/999,147. Additional target configurations presented in U.S. Patent Application Ser. No. 14/465,816 are microstructures comprising multiple x-ray generating materials, microstructures comprising alloys of x-ray generating materials, microstructures deposited with an anti-diffusion layer or an adhesion layer, microstructures with a thermally conducting overcoat, microstructures with a thermally conducting and electrically conducting overcoat, microstructured buried within a substrate and the like.

[0110] Other target configurations that may be used in embodiments of the invention, as has been described in the above cited US Patent Application Ser. No. 14/465,816, are arrays of microstructures that may comprise any number of conventional x-ray target materials patterned as features of micron scale dimensions on or embedded in a thermally conducting substrate, such as diamond or sapphire. In some embodiments, the microstructures may alternatively comprise unconventional x-ray target materials, such as tin (Sn), sulfur (S), titanium (Ti), antimony (Sb), etc. that have thus far been limited in their use due to poor thermal properties.

[0111] Other target configurations that may be used in embodiments of the invention, as has been described in the above cited US Patent Application Ser. No. 14/465,816, are arrays of microstructures that take any number of geometric shapes, such as cubes, rectangular blocks, regular prisms, right rectangular prisms, trapezoidal prisms, spheres, ovoids, barrel shaped objects, cylinders, triangular prisms, pyramids, tetrahedra, or other particularly designed shapes, including those with surface textures or structures that

enhance surface area, to best generate x-rays of high brightness and that also efficiently disperse heat.

[0112] Other target configurations that may be used in embodiments of the invention, as has been described in the above cited US Patent Application Ser. No. 14/465,816, are arrays of microstructures comprising various materials as the x-ray generating materials, including aluminum, titanium, vanadium, chromium, manganese, iron, cobalt, nickel, copper, gallium, zinc, yttrium, zirconium, molybdenum, niobium, ruthenium, rhodium, palladium, silver, tin, iridium, tantalum, tungsten, indium, cesium, barium, germanium, gold, platinum, lead and combinations and alloys thereof.

[0113] The embodiments described so far include a variety of x-ray target configurations that comprise a plurality of microstructures comprising x-ray generating material that can be used as targets in x-ray sources to generate x-rays with increased brightness.

2. Generic Considerations for a Linear Accumulation X-Ray Source.

[0114] FIG. 14 illustrates a collection of x-ray sub-sources arranged in a linear array. The long axis of the linear array runs from left to right in the figure, while the short axis would run in and out of the plane of the figure. Several x-ray generating elements 801, 802, 803, 804 ... etc. comprising one or more x-ray generating materials are bombarded by beams of electrons 1111, 1112, 1113, 1114, ... etc. at high voltage (anywhere from 1 to 250 keV), and form sub-sources that produce x-rays 818, 828, 838, 848, ... etc. Although the x-rays tend to be radiated isotropically, this analysis is for a view along the axis down the center of the linear array of sub-sources, where a screen 84 with an aperture 840 has been positioned.

[0115] It should be noted that, as drawn in FIG. 14, the aperture allows the accumulated zero-angle x-rays to emerge from the source, but in practice, an aperture which allows several degrees of x-rays radiated at $\pm 3^\circ$ or even at $\pm 6^\circ$ to the surface normal may be designed for use in some applications. It is generally preferred that the window be at normal or near normal incidence to the long axis of a linear array, but in some embodiments, a window tilted to an angle as large as 85° may be useful.

[0116] Assuming the i th sub-source 80i produces x-rays 8i8 along the axis to the right in FIG. 14, the radiation for the right-most sub-source as illustrated simply propagates to the right through free space. However, the x-rays from the other sub-sources are attenuated through absorption, scattering, or other loss mechanisms encountered while passing through whatever material lies between sub-sources, and also by divergence from the propagation axis and by losses encountered by passage through the neighboring sub-source(s) as well.

[0117] Using the definitions:

I_i as the x-ray radiation intensity 8i8 from the i th sub-source 80i;

$T_{1,0}$ as the x-ray transmission factor for propagation to the right of the 1st sub-source 801;

$T_{i,i-1}$ as the x-ray transmission factor for propagation from the i th sub-source 80i to the $i-1$ -th sub-source 80(i-1); and

T_i as the x-ray transmission factor for propagation through the i th sub-source 80i (with $T_0 \equiv 1$),

the total intensity of x-rays on-axis to the right of the array of N sub-sources can be expressed as:

$$\begin{aligned}
 I_{tot} = & I_1 \times T_{1,0} \\
 & + I_2 \times T_{2,1} \times T_1 \times T_{1,0} \\
 & + I_3 \times T_{3,2} \times T_2 \times T_{2,1} \times T_1 \times T_{1,0} \\
 & + I_4 \times T_{4,3} \times T_3 \times T_{3,2} \times T_2 \times T_{2,1} \times T_1 \times T_{1,0} \\
 & + \dots \\
 & + I_N \times T_{N,N-1} \times T_{N-1} \times T_{N-1,N-2} \times \dots \times T_2 \times T_{2,1} \times T_1 \times T_{1,0}
 \end{aligned} \quad [\text{Eqn. 3}]$$

making

$$I_{tot} = \sum_{i=1}^N I_i \prod_{j=0}^{i-1} T_j \prod_{k=0}^{i-1} T_{k+1,k} \quad [\text{Eqn. 4}]$$

[0118] For a source design in which all sub-sources produce approximately the same intensity of x-rays

$$I_i \approx I_0 \quad [\text{Eqn. 5}]$$

the total intensity becomes

$$I_{tot} = I_0 \sum_{i=1}^N \prod_{j=0}^{i-1} T_j \prod_{k=0}^{i-1} T_{k+1,k} \quad [\text{Eqn. 6}]$$

[0119] Furthermore, if the sub-sources are arranged in a regular array with essentially the same value for transmission between elements:

$$T_{a,a-1} = T_{2,1} , a > 1, \quad [\text{Eqn. 7}]$$

and if the sizes and shapes of the x-ray generating elements are similar enough such that the transmission through any given element will also be the same:

$$T_a = T_1 , a > 0 , \quad [\text{Eqn. 8}]$$

then the total intensity becomes

$$I_{tot} = I_0 T_{1,0} \left(\sum_{n=0}^{N-1} \left(T_1 T_{2,1} \right)^n \right) \quad [\text{Eqn. 9}]$$

[0120] Note that T_i and $T_{i,i-1}$ represent a reduction in transmission due to losses, and therefore always have values between 0 and 1. If N is large, the sum on the right can be approximated by the geometric series

$$\frac{1}{(1-x)} = \sum_{n=0}^{\infty} x^n \quad \text{for } |x| < 1 \quad [\text{Eqn. 10}]$$

making the approximate intensity

$$I_{tot} \approx I_0 T_{1,0} \frac{1}{(1 - T_1 T_{2,1})} \quad [\text{Eqn. 11}]$$

[0121] Note that this can also be used to estimate how many generating elements can be arranged in a row before losses and attenuation would make the addition of another x-ray generating element unproductive. For example, if the width of a generating element is μ_L , the 1/e attenuation length for x-rays, transmission through the element gives $T_1 = 1/e = 0.3679$. Assuming a transmission between elements of $T_{i,i-1} = T_{2,1} = 0.98$, this makes

$$I_{tot} \approx I_0 T_{1,0} \frac{1}{(1 - (0.3679)(0.98))} = I_0 T_{1,0} (1.564) \quad [\text{Eqn. 12}]$$

This means that a large number of elements with a width equal to the 1/e length could only improve the intensity by a factor of 1.564. For 2 elements (a total x-ray generation length of $2 \times \mu_L$), Eqn. 9 indicates that $I_{tot} \approx I_0 T_{1,0} (1.361)$, 87% of the estimated maximum from Eqn. 12, while for 3 elements (a total x-ray generation length of $3 \times \mu_L$), $I_{tot} \approx I_0 T_{1,0} (1.490)$, 95% of the estimated maximum, and for 4 elements (a total x-ray generation length of $4 \times \mu_L$), $I_{tot} \approx I_0 T_{1,0} (1.537)$, which is 98% of the estimated maximum degree of linear accumulation

from Eqn. 12. This suggests a general rule that linear accumulation near the maximum may be achieved from a total length of x-ray generating material of only $4 \times \mu_L$.

[0122] FIG. 15 illustrates the $1/e$ attenuation length for x-rays having energies ranging from 1 keV to 1000 keV for three x-ray generating materials: molybdenum (Mo), copper (Cu), tungsten (W); and from 10 keV to 1000 keV for three substrate materials: graphite (C), beryllium (Be) and water (H₂O). [The data presented here were originally published by B.L. Henke, E.M. Gullikson, and J.C. Davis, in “X-ray interactions: photoabsorption, scattering, transmission, and reflection at E=50-30000 eV, Z=1-92”, Atomic Data and Nuclear Data Tables vol. **54** (no.2), pp. 181-342 (July 1993), and may be also accessed at: henke.lbl.gov/optical_constants/atten2.html. Other x-ray absorption tables are available at: physics.nist.gov/PhysRefData/XrayMassCoef/chap2.html.]

[0123] The $1/e$ attenuation length μ_L for a material is related to the transmission factors above for a length L by

$$T_i = e^{-\alpha_i L} = e^{-L/\mu_L} \quad [\text{Eqn. 13}]$$

Therefore, a larger μ_L means a larger T_i .

[0124] As an example of using the values in FIG. 15, for 60 keV x-rays in tungsten, $\mu_L \approx 200 \mu\text{m}$, making the transmission of a $20 \mu\text{m}$ wide x-ray generating element

$$T_i = e^{-L/\mu_L} = e^{-20/200} = 0.905 \quad [\text{Eqn. 14}]$$

For 60 keV x-rays in a beryllium substrate, $\mu_L \approx 50,000 \mu\text{m}$, which makes the transmission of a $100 \mu\text{m}$ wide beryllium gap between embedded tungsten x-ray generating elements to be:

$$T_{i,i-1} = e^{-L/\mu_L} = e^{-100/50,000} = 0.998 \quad [\text{Eqn. 15}]$$

Therefore, for a periodic array of tungsten elements $20 \mu\text{m}$ wide embedded in a Beryllium substrate and spaced $100 \mu\text{m}$ apart, the best-case estimate for the on-axis intensity is:

$$I_{tot} \approx I_0 T_{i,0} \frac{1}{(1 - (0.905)(0.998))} = I_0 T_{i,0} (10.312) \quad [\text{Eqn. 16}]$$

which would represent an increase in x-ray intensity by an order of magnitude when compared to a single tungsten x-ray generating element.

3. X-Ray Source Controls.

[0125] There are several variables through which a generic linear accumulation source may be “tuned” or adjusted to improve the x-ray output. Embodiments of the invention may allow the control and adjustment of some, all, or none of these variables.

3.1. E-beam Variations.

[0126] In some embodiments, the beam or beams of electrons 111 or 1111, 1112, 1113, etc. bombarding the x-ray generating elements 801, 802, 803... etc. may be shaped and directed using one or more electron control mechanisms 70 such as electron optics, electrostatic lenses or magnetic focusing elements. Typically, electrostatic lenses are placed within the vacuum environment of the x-ray source, while the magnetic focusing elements can be placed outside the vacuum.

[0127] In many embodiments, the area of electron exposure can be adjusted so that the electron beam or beams primarily bombard the x-ray generating elements and do not bombard the regions in between the elements. A source having multiple electron beams that are used to bombard distinct x-ray generating elements independently may also be configured to allow a different accelerating voltage to be used with the different electron beam sources. Such a source 80-B is illustrated in FIG. 16. In this illustration, the previous high voltage source 10 is again connected through a lead 21-A to an electron emitter 11-A that emits electrons 111-A towards a target 1100-B. However, two additional “boosters” for voltage 10-B and 10-C are also provided, and these higher voltage potentials are connected through leads 21-B and 21-C to additional electron emitters 11-B and 11-C that respectively emit electrons 111-B and 111-C of different energies. Although the target 1100-B will usually be uniformly set to the ground potential, the individual electron beam sources used to target the different x-ray generating elements may be set to different potentials, and electrons of varying energy may therefore be used to bombard the different x-ray generating elements 801, 802, 803, ... etc.

[0128] This may offer advantages for x-ray radiation management, in that electrons of different energies may generate different x-ray radiation spectra, depending on the materials used in the individual x-ray generating elements. The heat load generated may also be managed through the use of different electron energies.

3.2. Material Variations.

[0129] Although it is simpler to treat the x-ray generating elements as identical units, and to have the intervening regions also be considered identical, there may be advantages in some embodiments to having variations in these parameters.

[0130] In some embodiments, the different x-ray generating elements may comprise different x-ray generating materials, so that the on-axis view presents a diverse spectrum of characteristic x-rays from the different materials. Materials that are relatively transparent to x-rays may be used in the position closest to the output window 840 (e.g. the element 801 furthest to the right in FIG. 14), while those that are more strongly absorbing may be used for elements on the other side of the array, so that they attenuate the other x-ray sub-sources less.

[0131] In some embodiments, the distance between the x-ray generating elements may be varied. For example, a larger space between elements may be used for elements that are expected to generate more heat under electron bombardment, while smaller gaps may be used if less heat is expected.

3.3. Rotating Anode Embodiments.

[0132] The target described above might also be used in an embodiment comprising a rotating anode, distributing the heat as the anode rotates. A system 580-C comprising these features is illustrated in FIGs. 17A – 17C. In this embodiment, many of the elements are the same as in a conventional rotating anode system, as was illustrated in FIG. 5A, but in the embodiment as illustrated, the rotating mechanism has been rotated 90° relative to the electron beam emitter 11-R and the electron beam 511-R.

[0133] The target in the embodiment as illustrated is a rotating cylinder 5100 mounted on a shaft 530. In one end of the cylinder 5100, a set 5710 of rings of x-ray generating material 5711 – 5717 have been embedded into a layer of substrate material 5000, with a gap between each ring. The “length” (parallel to the shaft axis in this illustration, and perpendicular to the local normal n in the region under bombardment) of each ring may be comparable to the length discussed for the set of microstructures illustrated in FIG. 10 (i.e. micron-scale), and the spacing may be comparable to L_{gap} (also micron-scale). The depth (i.e. parallel to the local normal n) into the substrate 5000 may also be comparable to the depth discussed in the previous embodiments (i.e. micron scale, and related to either the

penetration depth or the CSDA depth for either the x-ray generating material or the substrate.) The “width”, however, is the circumference, as the rings 5710 circle the entire cylinder 5100.

[0134] This substrate material 5000 may in turn be attached or mounted on a core support 5050 attached to the rotating shaft 530. The core support may comprise any number of materials, but a core of an inexpensive material with high thermal conductivity, such as copper, may be preferred. A solid core/substrate combination that comprises a single material may also be used in some embodiments. The substrate 5000 may be deposited using a CVD process, or pre-fabricated and attached to the core support 5050.

[0135] When bombarded with an electron beam 511-R, the portions of the set of rings 5710 of x-ray generating materials that are exposed will generate heat and x-rays 5588. X-rays radiated at a zero-angle (perpendicular to a local surface normal for the target in the region under electron bombardment) or near zero-angle may experience linear accumulation, and appear exceptionally bright. Embedding the set of rings 5710 of x-ray generating material into the substrate 5000 facilitates the transfer of heat away from the x-ray generating structures, allowing higher electron flux to be used to generate more x-rays without causing damage to the structures, as has been demonstrated for the non-rotating case.

[0136] It should be noted that the illustrations of FIGs. 17A – 17C are provided only to illustrate the functioning of an embodiment of the invention, and that the relative sizes, dimensions, and proportions of the rotating shaft 530, core support 5050, substrate 5000, and rings of x-ray generating material 5711 – 5717 should not be inferred from these drawings. The use of only seven rings in the illustration is also not meant to be limiting, as embodiments with any number of x-ray generating structures may be used.

[0137] In practical embodiments, the substrate thickness may range from a few microns to 200 microns, while the core may typically have a diameter of 2 cm to 20 cm. A cylinder in which the core and substrate are the same material may also be used in some embodiments. Various overcoats for electrical conduction and/or protection, as discussed for planar targets and illustrated in FIG. 13, may also be applied to embodiments having a rotating anode.

[0138] Although only parallel rings with zero take-off angle have been illustrated in FIGs. 17A – 17C, additional geometries for near-zero take-off angles, such as those using a

beveled surface, may have advantages. Likewise, other configurations for the x-ray generating materials may be used. FIG. 18 illustrates a target cylinder 5101 for a rotating anode comprising a set of parallel lines 5720 that have an orientation perpendicular to that used for the rings of FIG. 17B. Other target designs, such as checkerboards, grids, etc. as have been illustrated U.S. Provisional Patent Application Ser. No. 62/141,847 (to which the Parent Application of the Present Application claims the benefit of priority) as well various designs and structures illustrated in other planar embodiments of the present Application and the previously mentioned co-pending Applications may be used. Furthermore, additional elements found in other embodiments described in the present Application, such as focused electron beams and the like, different x-ray generating material selections and the like, the use of a powered x-ray generating material, etc., as well as those described the co-pending patent Applications to which it claims priority, may also be applied to rotating anode embodiments.

3.4. Materials Selection for the Substrate.

[0139] For the substrate of a target with microstructures of x-ray generating material, as shown above it is preferred that the transmission of x-rays T for the substrate be near 1. For a substrate material of length L and linear absorption coefficient α_s ,

$$T = e^{-\alpha_s L} = e^{-L/\mu_L} \quad [\text{Eqn. 17}]$$

where μ_L is the length at which the x-ray intensity has dropped by a factor of $1/e$.

[0140] Generally,

$$\mu_L \propto X^3 / Z^4 \quad [\text{Eqn. 18}]$$

where X is the x-ray energy in keV and Z is the atomic number. Therefore, to make μ_L large (i.e. make the material more transparent), higher x-ray energy is called for, and a lower atomic number is highly preferred. For this reason, both beryllium ($Z=4$) and carbon ($Z=6$) in its various forms (e.g. diamond, graphite, etc.) may be desirable as substrates, both because they are highly transparent to x-rays, but also because they have high thermal conductivity (see Table I).

4. Design Guidelines for Structured Targets.

[0141] The embodiments of the invention disclosed in this Application can be especially suitable for making a high brightness x-ray source for use at one or more predetermined low take-off angles. In some embodiments, the arrangement of discrete structures of x-ray generating material can be arranged to increase the x-ray radiation into a predetermined cone of angles around a predetermined take-off angle. Such a predetermined cone can be matched to the acceptance angles of a defined x-ray optical system to increase or maximize the useful x-ray intensity that may be delivered to a sample in applications such as XRD, XRF, SAXS, TXRF, especially, with microbeams, such as microXRD, microXRF, microSAXS, microXRD, etc. Examples of such an x-ray optical system is one having a monocapillary x-ray optical element with a defined inner reflective surface, such as a paraboloidal collimator or a dual paraboloidal or ellipsoidal focusing surface.

[0142] In other embodiments, the arrangement of discrete structures of x-ray generating material can be arranged to increase the x-ray radiation into a predetermined fan of angles around a predetermined take-off angle. Such a distribution of x-rays may be matched to other x-ray optical elements designed to produce x-ray beams with a line profile or collimated to form a parallel beam instead of a focused spot.

[0143] The design of the layout of the x-ray generating elements in the target can be optimized to increase the x-rays radiated in specific directions using two factors. One is the management of the thermal load, so that heat is efficiently transported away from the x-ray generating elements. With effective thermal transfer, the x-ray generating elements can be bombarded with an electron beam of even greater power density to produce more x-rays. The second is the distribution of the x-ray generating materials such that the self-absorption of x-rays propagating through the remaining volume of x-ray generating material is reduced and linear accumulation of x-rays is optimized.

4.1. An Example: Microstructured Target for a Conical X-ray Beam

[0144] FIGs. 19A – 19C illustrate an example of a target 1100-T comprising a set 710 of embedded microstructures of x-ray generating material 711, 712... 717 embedded within a substrate 1000, similar to the target of FIG. 10. As illustrated, the microstructures 711 – 717 are embedded near a shelf 1002 at the edge 1003 of the surface of the substrate 1000. When bombarded by electrons 111 within a vacuum chamber, the x-ray generating material produces x-rays 2088.

[0145] For the target 1100-T as illustrated, there is a local surface in the area of the x-ray generating elements that has a surface normal n . This defines an axis for the dimension of depth D into the target for determining the depth of the x-ray generating materials. This axis is also used to measure the electron penetration depth or the electron continuous slowing down approximation depth (CSDA depth).

[0146] For the target as illustrated, there is furthermore a predetermined take-off direction (designated by ray 88-T) for the downstream formation of an x-ray beam. This take-off direction is oriented at an angle θ_T relative to the local surface, and the projection of this ray onto the local surface (designated by ray 88-S) in the plane that contains both the take-off angle and the surface normal is a determinant of the dimension of length L for the target. The final dimension of width W is defined as the third spatial dimension orthogonal to both the depth and the length directions.

[0147] As illustrated, the set of discrete structures of x-ray generating material is in the form of a linear array of x-ray generating microstructures, each of length L_M , width W_M , and depth D_M , the same as was that illustrated in FIG. 10. As illustrated, $W_M = D_M$, but in the general case, the width and depth need not be identical. In the target as illustrated in FIG. 19C, the microstructures are aligned along an axis parallel to the length L dimension, and are separated from each other by a gap L_{Gap} , so that the total length of the x-ray generating volume comprising 7 microstructures of x-ray generating material is $L_{Tot} = 7 L_M + 6 L_{Gap}$.

[0148] It should be noted that these dimensions of depth, length and width in a given target may or may not correspond to those that might be intuited merely from the layout of the discrete structures of x-ray generating material. As has already been illustrated, discrete structures of x-ray generating material may be laid out in 1-dimensional and 2-dimensional arrays, grids, checkerboards, staggered and buried structures, etc. and the

alignment and relative orientation of these physical arrays and patterns with the predetermined take off angle and the surface normal may or may not be parallel. As defined in these embodiments, the coordinates of depth, length and width are defined only by the surface normal and the predetermined take-off angle.

[0149] As illustrated in FIG. 19A – 19C, a predetermined set of cone angles is defined, centered around the take-off angle θ_T . A ray propagating along the innermost portion of the cone makes an angle θ_1 with respect to the take off angle, while a ray propagating along the outermost portion of the cone makes an angle θ_2 with respect to the take off angle. These cone angles are generally quite small (less than 50 mrad), and the take-off angle is generally between 0° to 6° (0 to 105 mrad).

[0150] The actual design of the x-ray target may be more easily described using the concept of an “x-ray generating volume”, as discussed further below. This is the volume of the target from which the substantial majority of the x-rays of a desired energy will be radiated. In the embodiments of the invention, there are four primary factors that may affect the design rules for the structure of x-ray generating material within the x-ray generating volume that may be applied in embodiments of the invention to improve the x-ray brightness radiated into this predetermined cone. These four factors are:

- the volume fraction of x-ray generating material;
- the relative thermal properties of the x-ray generating material and substrate;
- the distance of propagation of the X-rays through x-ray generating material; and
- the depth of x-ray generation.

4.1.1. X-ray Generating Volume.

[0151] The “x-ray generating volume” of a target comprising discrete structures of x-ray generating material is the volume of the target that, when bombarded with electrons, generates x-rays of a desired energy. The energy is typically specified as the characteristic x-ray radiation generated by specific transitions in the selected x-ray generating material, although for certain applications, spectral bandwidths of continuum x-rays from the x-ray generating material may also be designated.

[0152] Two “volumes” must be considered to define the “x-ray generating volume”: a “geometric volume” encompassing the x-ray generating material, and the “electron

excitation volume” encompassing the region in which electrons deliver enough energy to generate x-rays.

4.1.1A. Geometric Volume

[0153] The “geometric volume” for the x-ray generating material is defined as the minimum contiguous volume that completely encompasses a given set of discrete structures of x-ray generating material and the gaps between them.

[0154] For the x-ray generating structures of FIGs. 19A – 19C, also reproduced FIGs. 20A – 20C, the “geometric volume” 7710 is a rectangle surrounding the microstructures of x-ray generating material.

[0155] For other configurations, such as those shown in FIG. 21A – 21C, the “geometric volume” may be more complex. In this example, a set 2710 of non-uniform structures of x-ray generating material 2711, 2712... 2717 are embedded within a substrate 1000, in which structures are tapered smaller as they approach the edge 1003 of the substrate. The “geometric volume” 7711 for this case is not a rectangle, but a tapered polyhedron having square ends of different sizes.

4.1.1B. Electron Excitation Volume.

[0156] The “electron excitation volume” is the volume of the target in which electrons deliver enough energy to generate x-rays of a predetermined desired energy.

[0157] FIG. 22A – 22C illustrate this situation. In FIGs. 22A – 22C, electron beam 111 bombards a portion of the same target comprising a set 710 of x-ray generating materials embedded in a substrate 1000 – the same target layout as was shown in FIGs. 19A – 19C, and 20A – 20C. However, the extent of the electron beam does not encompass the entire set of structures, but has a beam width of W_e less than W_M , and a beam length L_e which is less than L_{Tot} and is also not exactly aligned with the edge of the target structures. The overall area of exposure at the surface is therefore the area of the electron beam at the intersection with the surface (the electron beam “footprint”), defined at some threshold value, such as the full-width-at half-maximum (FWHM) value or the 1/e value relative to the peak intensity. In general, the defined boundary for the footprint will be defined at the contour where the electron intensity is at 50% of the maximum electron intensity.

[0158] The electron beam bombarding the target may have various sizes and shapes, depending on the electron optics selected to direct and shape the electron beam. For example, the electron beam may be approximately circular, elliptical, or rectangular. Various accelerating voltages may be used as well, although generally the accelerating voltage will be selected to be at least twice that needed to produce x-rays of a given energy (e.g. to produce x-rays with an energy of ~ 8 keV, the accelerating voltage is preferred to be at least 16 keV).

[0159] If the entire region of x-ray generating structures is bombarded with an equivalent footprint of electrons of high energy, the x-ray generating volume may be identical to the “geometric volume” as described above. However, in some cases, the depth of the microstructured x-ray generating material D_M may be significantly deeper than the electron penetration depth into the substrate, which may be estimated using Potts’ Law (as discussed above), or deeper than the continuous slowing down approximation (CSDA) range (CSDA values normalized for element density may be computed using the NIST website physics.nist.gov/PhysRefData/Star/Text/ESTAR.html). In such cases, the deeper regions of x-ray generating material may be relatively unproductive in generating x-rays, and the x-ray generating volume is preferably defined by the area overlap of the electron footprint upon the sample with the minimal geometric area containing the microstructures and the electron penetration depth of the electrons into the substrate. For 60 keV electrons bombarding copper (density ~ 8.96 g/cm³) the electron penetration depth by Potts’ Law is estimated to be ~ 5.2 microns, while the CSDA depth is ~ 10.6 microns. For a diamond substrate (density ~ 3.5 g/cm³), the Potts’ Law penetration depth is ~ 15.3 microns, while the CSDA depth for the diamond substrate is ~ 18.9 microns.

[0160] In some embodiments, the depth of the x-ray generating structures D_M measured from the target surface may be limited to be less than the penetration depth of the electrons into the x-ray target substrate material. In most cases (due to the typically lower mass density of the x-ray substrate relative to the x-ray generating material), the entire depth of x-ray generating material will be generating x-rays. In some embodiments, the depth of the x-ray generating structures D_M measured from the target surface may be some multiple (e.g. 1x – 5x) of the penetration depth of the electrons into the x-ray target substrate material. In this case, the depth D_P of the electron excitation volume 7770-E in which x-rays are generated will be less than D_M , as illustrated in FIGs. 22A – 22C, and the depth D_P will be

defined as a predetermined number related to either the electron penetration depth or the CSDA depth. (Note: the depth dimension is defined as parallel to the surface normal, and if the electron beam is incident on the target surface at an angle ψ other than 0° (normal incidence), the depth D_p of the electron excitation volume must be modified from the normal incidence penetration depth by a factor of $\cos \psi$.)

[0161] In other embodiments, the depth of the x-ray generating structures D_M measured from the target surface may be limited to be less than the penetration depth of the electrons into the x-ray generating material. This may include 1X the penetration depth, or in some cases, preferably a fraction of the penetration depth such as 1/2 or 1/3 of the penetration depth.

[0162] For some embodiments, the depth D_p of the electron excitation volume will be defined as being equal to half the penetration depth of the target X-ray generating material, since this is the depth over which the electrons will generate more characteristic x-rays. (See the discussion of FIG. 2 above for more on the topic of characteristic x-ray generation.

4.1.1C. Synthesis of the X-ray Generating Volume.

[0163] For any general embodiment, the x-ray generating volume will be defined as the volume overlap of the “geometric volume” for the x-ray generating material within the target and the “electron excitation volume” for electrons of a predetermined energy and known penetration depth and CSDA depth for materials of the target.

4.1.2. Design Rules for Volume Fraction.

[0164] The volume fraction of the x-ray generating volume is defined as the ratio of the volume of the x-ray generating material within the x-ray generating volume to the overall x-ray generating volume. A typical prior art x-ray target with a uniform target of x-ray generating material will have a volume fraction of 100%. Targets such those illustrated in FIG. 10, with $L_M = 1$ micron and $L_{Gap} = 2$ microns, have a volume fraction of ~37 %.

[0165] A general rule for the x-ray sources according to the invention disclosed here is that the volume fraction of the x-ray generating volume be between 10 and 70%, with the non-x-ray generating portion being filled with material of a high thermal conductivity.

The regions of non-x-ray generating material serve to conduct the heat away from the x-ray generating structures, enabling bombardment with an electron beam of higher power, thereby producing more x-rays.

[0166] The ideal volume fraction for a target typically depends on the relative thermal properties of the x-ray generating material and the substrate material in the x-ray generating volume. If the target is fabricated by embedding discrete structures of x-ray generating material with moderate thermal properties into a substrate of high thermal conductivity, good thermal transfer is generally achieved. If the thermal transfer between the x-ray generating material and the substrate is poor (for example, in circumstances of when the x-ray generating material has poor thermal properties), a smaller volume fraction may be desired. In general, for the embedded target structures described herein, a volume fraction of 30% - 50% is preferred.

[0167] It should be noted that in some embodiments, the discrete x-ray structures are not manufactured through etching or ordered patterning processes but instead formed using less ordered discrete structures, such as powders of target materials. FIG. 23 illustrates a target fabricated by such a process. In a substrate 1000, a groove 7001 or set of grooves may be formed using standard substrate patterning techniques. The groove 7001 is then filled with particles of a powder of x-ray generating material 7077. The particles 7077 may be of a predetermined average size and shape, so that a measured volume of the material may be used to produce a desired volume fraction within the groove.

[0168] Once the particles of x-ray generating material have been placed in the groove, the gaps between particles 7006 can be filled with a coating of material deposited by chemical vapor deposition (CVD) processes. This provides the thermal dissipation for the heat produced in the x-ray generating target structures. When bombarded by electrons 111, the x-ray generating material will produce x-rays 8088. As long as the space between particles is small, and the depth of the groove is less than half the penetration depth of the electrons into the substrate, the x-ray generating volume 7070 will be the overlap of the groove (defining the geometric volume) and the projection of the footprint of the electron beam at the surface.

[0169] In some embodiments, the powders may be pressed into an intact ductile substrate material. In some embodiments, additional overcoats as described for more regular structures and illustrated in FIG. 13 may be used for targets fabricated using powders as well.

[0170] For a target formed using a powder of x-ray generating material, the substrate is preferably a material with high thermal conductivity, such as diamond or beryllium, and the filling material is a matching material (e.g. diamond) deposited by CVD.

4.2.3. Design Rules for Thermal Properties.

[0171] The x-ray source target substrate material is preferred to have superior thermal properties, particularly its thermal conductivity, in respect to the x-ray generating material. Moreover, it is preferred that substrate materials of the target limit the self-absorption of x-rays produced in the target along the low take-off angle. In many embodiments, this leads to the selection of a substrate material having low atomic number, such as diamond, beryllium, sapphire, or some other carbon-based material.

[0172] For some materials, such as diamond, the thermal conductivity is severely reduced in very thin samples of the material. There may therefore be a minimum thickness required for the space between structures of x-ray generating material.

[0173] In general, for diamond having embedded structures of x-ray generating material, suitable results have been achieved when the thickness of the diamond between structures of x-ray generating material is 0.5 micrometer or more.

[0174] Likewise, if the discrete structures of x-ray generating material are too thick, heat cannot transfer efficiently from the center to the outside, and there is therefore a practical limit on how thick a given structure of x-ray generating material should be.

[0175] In general, when being embedded into diamond, suitable results have been achieved when the thickness of the x-ray generating structures is 10 micrometers or less.

4.1.4. Design Rules based on Propagation Length.

[0176] As described previously, there will be a total length for x-ray generation after which additional x-rays generated cease to contribute additional x-rays to the output, due to reabsorption. There is therefore an upper bound on the length ΣL_M of the x-ray generating material within the x-ray generating volume.

[0177] For a given x-ray energy, which in general may correspond to a characteristic line of the selected x-ray generating material, μ_L is defined to be the 1/e attenuation length for x-rays of that energy in the same material. Values for this number have been illustrated in FIG. 15, and numerical values are shown in Table III below for a few commonly used x-ray generating materials. The x-ray energies are taken from the NIST website physics.nist.gov/PhysRefData/XrayTrans/Html/search.html and the attenuation lengths are calculated using the same sources as were used for the data in FIG. 15.

Table III: 1/e Attenuation lengths for various x-ray transitions

X-ray Transition	X-ray Energy (keV)	μ_L (μm)
Cu $K\alpha$	8.05	21.8
Mo $K\alpha$	17.48	55.1
W $K\alpha$	59.32	136.3

[0178] As a general rule, the propagation path through x-ray generating material for any given x-ray path should be less than $4 \times \mu_L$. For target structures such as the powder structure in FIG. 23, to insure that no path through the x-ray generating volume is significantly longer than the upper bound for x-ray production, a design rule that the entire length of the groove L_{Tot} be less than $4 \times \mu_L$ may be followed. In other embodiments, a design rule that L_{Tot} be less than $(4 \times \mu_L)$ divided by the volume fraction may be followed.

[0179] For more defined discrete target structures, such as that illustrated in FIG. 19C, a design rule limiting the length of the sum of segments in which a predetermined ray overlaps the x-ray generating material may be set.

[0180] In FIG. 19C, the designated ray is the ray 88-T corresponding to the take-off angle at θ_r , shown relative to a ray 88-M running through the midpoint of the x-ray generating volume. The path of this ray 88-T through the x-ray generating volume 7710-E has several segments of overlap 711-S, 712-S, ..., 717-S corresponding to the overlap with the slabs 711, 712, ..., 717 of x-ray generating material. A general design rule can be stated that, for any ray parallel to the take-off angle ray, the sum of the segments of overlap with the x-ray generating material within the x-ray generating volume must be smaller than $4 \times \mu_L$. In

some embodiments, this sum of the segments of overlap with the x-ray generating material within the x-ray generating volume must be smaller than $2 \times \mu_L$.

[0181] Although FIG. 19C uses the ray of the take-off angle as a design rule, other embodiments may instead have a restriction on the sum of segments of overlap for a ray within the cone of propagation, i.e. between angles θ_1 and θ_2 .

[0182] Such a target design is illustrated in FIGs. 24A – 24C. In this embodiment, a number of microstructures 2110 in the form of microslabs of x-ray generating material 2111, 2112, ..., 2116, ... etc. are embedded in a substrate 2000, near the edge 2003 of a shelf 2002 in a substrate 2000, but the orientation of the microstructures has the narrowest dimension aligned with the “width” direction and the longest dimension along the length dimension. The geometric volume 2770 in this example is a rectangle of volume $L_{Tot} \times W_{Tot} \times D_M$.

[0183] If the take-off angle is in the plane of the microstructures, the path for x-rays at or near the take-off angle may be longer than the reabsorption upper bound. However, for x-rays emerging from the sides of the microstructures, low attenuation through the surrounding substrate and other x-ray microstructures may be achieved. The spacing between the microstructures may be adjusted so that x-rays emerging at the maximum cone angle θ_2 in the plane orthogonal to the plane of the take-off angle (i.e. in the plane of FIG. 24A) intersect a certain number of additional microstructures, achieving linear accumulation, but do not exceed the reabsorption upper bound. The appropriate metric for the limitation on length segments will therefore be for rays at angles corresponding to certain cone angles out of the plane of the microstructures, and not the take-off angle.

[0184] Note that these cone angles need not be in any particular plane, and therefore a design rule limiting the length of overlap must apply to certain rays within the cone, preferably those out of the plane of orientation for the microstructures. In some embodiments, a design rule limiting the length of the sum of segments will apply to any cone angle within a predetermined subset of cone angles. In some embodiments, a design rule limiting the length of the sum of segments will apply to a majority of cone angles.

[0185] A general design rule can be stated that, for any ray within a predetermined subset of cone of angles greater than or equal to θ_1 and less than or equal to θ_2 relative to the take-off angle ray, the sum of the segments of overlap with the x-ray generating material within the x-ray generating volume must be smaller than $4 \times \mu_L$. Note that for prior

embodiments, this design rule may also be used rather than using the ray along the take-off angle to define the amount of x-ray generating material within a given x-ray generating volume.

[0186] Design rules may also be placed on having a minimum length for sums of segments of overlap, to ensure that at least some accumulation of x-rays may occur. For some embodiments, the sum of the segments of overlap with the x-ray generating material within the x-ray generating volume must be greater than $0.3 \times \mu_L$. For other embodiments, the sum of the segments of overlap with the x-ray generating material within the x-ray generating volume must be greater than $1.0 \times \mu_L$. For other embodiments, the sum of the segments of overlap with the x-ray generating material within the x-ray generating volume must be less than $1 \times \mu_L$ and in other embodiments this may be $2.0 \times \mu_L$.

4.1.5. Design Rules for Depth.

[0187] As discussed above, the depth D_M of the structures of x-ray generating material may be determined by any number of factors, such as the ease of reliably manufacturing embedded structures of certain dimensions, the thermal load and thermal expansion of the embedded structures, a minimum thickness to minimize source degradation due to delamination or evaporation, etc.

[0188] However, creating structures with a depth D_M significantly deeper than the electron penetration depth into the substrate will generally result in deep regions that are unproductive in generating x-rays. For 60 keV electrons bombarding copper (density $\sim 8.96 \text{ g/cm}^3$) the electron penetration depth by Potts' Law is estimated to be ~ 5.2 microns, while the CSDA depth is ~ 10.6 microns. For a diamond substrate (density $\sim 3.5 \text{ g/cm}^3$), the Potts' Law penetration depth is ~ 15.3 microns, while the CSDA depth for the diamond substrate is ~ 18.9 microns.

[0189] As a general design rule, the depth of the x-ray structures D_M measured from the target surface should be limited to be less than 5 times the penetration depth of the electrons into the x-ray target substrate material. This ensures that the depth of the structures of x-ray generating material, which typically have poorer thermal properties than the substrate, is minimized, as typically only the portion closer to the surface is efficient at generating characteristic x-rays. Although some x-rays are generated at lower depths, there is

also associated heat generation. In some embodiments, the depth of the x-ray generating material is preferred to be a fraction (e.g. 1/2) of the electron penetration depth in the x-ray generating material, providing the overlap of electron excitation and x-ray generating material primarily in the zone in which most of the characteristic x-rays are generated (see previous discussion of FIGs. 2, 8 & 9). In some embodiments, the depth of the x-ray generating material is preferred to be a fraction (e.g. 1/2) of the electron penetration depth in the substrate material. In some embodiments, the depth of the x-ray generating material is preferred to be half of the CSDA depth in the substrate material.

4.2. Relation of the X-ray Generating Volume to Take-off Angle.

[0190] Conventional reflection-type x-ray target geometries are often arranged, such that the x-ray beam emitted is centered along a take-off angle of $\sim 6^\circ$ measured from the x-ray target surface tangent. This angle is typically selected in an effort to both minimize apparent x-ray source size (smaller at lower take-off angles) and minimize self-attenuation by the x-ray target (larger at lower take-off angles).

[0191] The disclosed embodiments of the invention are preferably operated at take-off angles less than or equal to 3° , and for some embodiments at 0° take-off angle, substantially lower than for conventional x-ray sources. This is enabled by the structured nature of the x-ray source and the incorporation of an x-ray substrate, as discussed above, comprised of a material or structure that reduces or minimizes self-absorption of the x-ray energies of interest generated by the x-ray target.

[0192] Such a structured target is especially useful as a distributed, high-brightness source for use in systems that make use of an x-ray beam having the form of an annular cone. FIG. 25 illustrates the matching of the annular cone as defined in the previous embodiments with an aperture or window 2790 and/or beam stop 2794 in the system.

[0193] This annular output can be selected to match the acceptance angle of an x-ray optical element, such as a capillary optic with a reflecting inner surface used for directing (e.g. focusing or collimating) the generated x-ray beam for downstream applications. The predetermined cone of x-rays generated by the x-ray source can be defined to correspond to the angles and dimensions of such downstream optical elements. Likewise, a central beamstop to block the x-rays propagating at the take-off angle θ_T (which typically will not be

collected by the downstream optical elements such as monocapillaries) can also be used, with the propagation angles blocked by the beam stop being those that correspond to the inner diameter of the predetermined annular x-ray cone. In some embodiments, annular cones may be defined by the acceptance angles of downstream optics, i.e. by the numerical aperture of such optics, or other parameters that may occur in such systems. Matching the volume to, for example, the depth-of-focus range for a collecting optic or to the critical angle of the reflecting surface of a collecting optic may maximize the number of useful x-rays, while limiting the total power that must be expended to generate them.

[0194] The angular range for the annular cone of x-rays is generally specified by having the inner cone angle θ_1 being greater than 2 mrad relative to the take-off angle, and having the outer cone angle θ_2 be less than or equal to 50 mrad relative to the take-off angle.

4.3. Rotating Anodes.

[0195] The previous discussion on take-off angles and cones of annular x-rays may also be applied to rotating anodes.

[0196] FIG. 26 presents a cross-section view of a rotating anode in the form of a cylinder 5102 as may be inserted into a system as was illustrated in FIG. 17A. As in the embodiment of FIGS. 17A – 17C, the cylinder 5102 is mounted on a rotating shaft 530, and has a core 5050 of a thermally conducting material such as copper.

[0197] On the outer surface of the cylinder, a layer of substrate material 5000 such as diamond or CVD diamond has been formed, and embedded in this substrate are a number of rings 5711, 5712, ..., 5717 comprising x-ray generating material. As before, the “length” (parallel to the shaft axis in this illustration, and perpendicular to the local normal n in the region under bombardment) of each ring may be comparable to the length discussed for the set of microstructures illustrated in FIG. 10 (i.e. micron-scale), and the spacing may be comparable to L_{Gap} (also micron-scale). The depth (i.e. parallel to the local normal n) into the substrate 5000 may also be comparable to the depth discussed in the previous embodiments (i.e. micron scale, and related to either the penetration depth or the CSDA depth for either the x-ray generating material or the substrate.) The “width”, however, is the circumference, as the rings 5710 circle the entire cylinder 5100.

[0198] When a portion of the x-ray generating structures are bombarded by electrons 511-R, an x-ray generating volume 5070 is formed, generating x-rays 5088. Although x-rays may be radiated in many directions, for this system, as with the systems illustrated in FIGs. 19A – 19C, a predetermined take-off angle θ_T may be designated, along with a cone of angles ranging from θ_1 to θ_2 defined relative to the take-off angle. These angles are generally selected to correspond to x-rays that will be collected downstream to form a beam for use in x-ray optical systems. For the example illustrated in FIG. 26, the take-off angle is at 0° , making use of the x-rays that linearly accumulate through the set 5710 of rings comprising x-ray generating material. To reduce the attenuation of x-rays in the substrate 5000, the cylinder 5102 may additionally have a notch 5002 near the x-ray generating rings 5710, comparable to the shelf illustrated in the previous planar target configurations.

[0199] FIG. 27 presents a cross-section view of another embodiment of a rotating anode in the form of a cylinder 5105 as may be inserted into a system as was illustrated in FIG. 17A. As in the embodiment in FIG. 26, the cylinder 5105 is mounted on a rotating shaft 530, with a conducting core 5050 and an outer coating of a substrate material 5005, in which a set 5720 of rings comprising x-ray generating material 5721, 5722, ..., 5726 are embedded.

[0200] However, in the embodiment as illustrated, the cylinder is beveled at an angle in the region of the x-ray generating volume, and the take-off angle is at a non-zero angle θ_T , similar to the configuration for the planar geometry of FIG. 19C. The bevel angle is selected so that linear accumulation through the set 5720 of rings may still occur.

[0201] Also illustrated in this embodiment, the cylinder 5105 may also be fabricated with an interface layer 5003, which may provide a coupling between the beveled substrate 5005 and the core 5055.

[0202] Other rotating anode designs, such as patterns of lines, checkerboards, grids, etc. as have been illustrated U.S. Provisional Patent Application Ser. No. 62/141,847 (to which the Parent Application of the Present Application claims the benefit of priority) as well as various designs and structures illustrated in other planar embodiments of the present Application and the previously mentioned co-pending Applications may be used in these configurations as well. These rotating anode embodiments may additionally be fabricated

using conducting and/or protective overcoats, as was previously discussed for use with planar targets.

5. Limitations and Extensions.

[0203] With this application, several embodiments of the invention, including the best mode contemplated by the inventors, have been disclosed. It will be recognized that, while specific embodiments may be presented, elements discussed in detail only for some embodiments may also be applied to others. Also, details and various elements described as prior art may also be applied to various embodiments of the invention.

[0204] While specific materials, designs, configurations and fabrication steps have been set forth to describe this invention and the preferred embodiments, such descriptions are not intended to be limiting. Modifications and changes may be apparent to those skilled in the art, and it is intended that this invention be limited only by the scope of the appended claims.

[0205] All elements, parts and steps described herein are preferably included. It is to be understood that any of these elements, parts and steps may be replaced by other elements, parts and steps or deleted altogether as will be obvious to those skilled in the art.

[0206] Broadly, this writing discloses at least the following: A compact source for high brightness x-ray generation is disclosed. The higher brightness is achieved through electron beam bombardment of multiple regions aligned with each other to achieve a linear accumulation of x-rays. This may be achieved through the use of x-ray targets that comprise microstructures of x-ray generating materials fabricated in close thermal contact with a substrate with high thermal conductivity. This allows heat to be more efficiently drawn out of the x-ray generating material, and allows bombardment of the x-ray generating material with higher electron density and/or higher energy electrons, leading to greater x-ray brightness. The orientation of the microstructures allows the use of a take-off angle at or near 0°, allowing the accumulation of x-rays from several microstructures to be aligned and be used to form a beam in the shape of an annular cone.

Concepts

This writing also presents at least the following concepts.

1. A high brightness x-ray source comprising:
 - a vacuum chamber;
 - and, within the vacuum chamber,
 - at least one electron beam emitter; and
 - at least one target
 - comprising a substrate comprising a first selected material;
 - said target having a predetermined surface facing the electron beam emitter,
 - and having, within the target and adjacent to said predetermined surface,
 - a contiguous x-ray generating volume
 - having an orthogonal length and width
 - defined in a plane perpendicular to the normal of said predetermined surface,
 - and a depth into the target defined as parallel to the normal of said predetermined surface;
 - said x-ray generating volume comprising:
 - a plurality of discrete structures comprising a second selected x-ray generating material
 - that make up a predetermined volume fraction
 - of more than 10% and less than 70% of the x-ray generating volume;
 - said source additionally having an x-ray beam axis
 - selected to have a take-off angle of less than 6 degrees;
 - and, for any ray oriented parallel to the x-ray beam axis
 - that overlaps with the x-ray generating volume,
 - the sum of the lengths of the segments of said ray
 - that overlap x-ray generating material in the x-ray generating volume
 - is less than a predetermined overlap length.

2. The x-ray source of Concept 1, in which
the first selected material is selected from the group consisting of:
beryllium, diamond, polycrystalline diamond, diamond-like carbon, graphite, silicon,
boron nitride, silicon carbide, and sapphire.
3. The x-ray source of Concepts 1 or 2, in which
the x-ray generating volume is defined by the overlap
of a predetermined geometric volume
that includes the plurality of discrete structures
with a predetermined electron excitation volume
that will occur when the target is bombarded
with a predetermined pattern of electron beam
from the electron beam emitter.
4. The x-ray source of Concept 3, in which
the predetermined volume fraction of x-ray generating material
is between 30 and 50% of the x-ray generating volume.
5. The x-ray source of Concepts 3 or 4, in which
the take-off angle is less than 3 degrees.
6. The x-ray source of Concepts 3 through 5, in which
the length of the x-ray generating volume
that intersects a plane orthogonal to the target surface
and containing the x-ray beam axis
is greater than or equal to 1 micron and less than or equal to 500 microns.
7. The x-ray source of Concepts 3 through 6, in which
the discrete structures comprising a second selected x-ray generating material
are formed from a powder of the selected x-ray generating material
that has been deposited into a recessed region formed in the substrate.

8. The x-ray source of Concepts 3 through 7, in which
the discrete structures comprising a second selected x-ray generating material
are embedded into the substrate of first selected material, such that
the x-ray generating volume comprises
both the first selected material
and the second selected x-ray generating material.
9. The x-ray source of Concepts 3 through 8, in which
the length for any one of the discrete structures
along the x-ray beam axis
is less than or equal to 10 micron.
10. The x-ray source of Concepts 3 through 9, in which
the separation distance between any two of the discrete structures
is greater than or equal to 0.5 micron and less than or equal to 10 microns.
11. The x-ray source of Concepts 3 through 10, in which
the predetermined geometric volume is defined as the contiguous volume
both containing the plurality of discrete structures
and having minimal surface area.
12. The x-ray source of Concepts 3 through 11, in which
the boundary in the length and width dimensions
of the predetermined electron excitation volume
is defined by the half-maximum electron intensity.
13. The x-ray source of Concepts 3 through 12, in which
the second selected x-ray generating material is selected from the group consisting of:
aluminum, titanium, vanadium, chromium, manganese, iron, cobalt, nickel, copper,
gallium, zinc, yttrium, zirconium, molybdenum, niobium, ruthenium, rhodium,
palladium, silver, tin, iridium, tantalum, tungsten, indium, cesium, barium,
germanium, gold, platinum, lead, and combinations and alloys thereof.

14. The x-ray source of Concept 13, in which
an x-ray energy corresponding to the selected second x-ray generating material
is selected,
and said second x-ray generating material has a linear attenuation length μ_L
corresponding to said x-ray energy,
and in which the predetermined overlap length
is less than or equal to 4 times μ_L .
15. The x-ray source of Concept 14, in which
electrons from the electron beam emitter are selected to have a energy
greater than twice said x-ray energy; and
the depth of the electron exposure volume
is equal to the penetration depth for the electrons of a selected energy
in the first selected material.
16. The x-ray source of Concepts 1 through 6 and 8 through 15 , in which
the plurality of discrete structures are arranged in a linear array.
17. The x-ray source of Concepts 1 through 16, additionally comprising
at least one overcoat having a thickness of less than 20 microns
covering at least the discrete structures of the target.
18. The x-ray source of Concept 17, in which
the material of the at least one overcoat is selected from the group consisting of:
beryllium, diamond, polycrystalline diamond, CVD diamond, diamond-like carbon,
graphite, silicon, boron nitride, silicon carbide, and sapphire.
19. The x-ray source of Concept 17, in which
the material of the at least one overcoat is selected from the group consisting of:
graphene, silver, copper, gold, tungsten, aluminum, chromium, tin, and titanium.

20. The x-ray source of Concepts 1 through 19, additionally comprising:
a mechanism to rotate the target
while the target is being bombarded with electrons from said electron beam emitter.
21. The x-ray source of Concept 20, in which
the target is cylindrically symmetric, and
the substrate of the target is attached to a supporting core.
22. The x-ray source of Concept 21, in which
the supporting core comprises copper.
23. The x-ray source of Concepts 21 or 22, in which
the substrate has a thickness
greater than or equal to 5 micrometers
and less than or equal to 2 millimeters.
24. The x-ray source of Concepts 21 or 22, in which
the radius of curvature of the substrate is greater than 20 millimeters.

25. A high brightness x-ray source comprising:
- a vacuum chamber;
 - and, within the vacuum chamber,
 - at least one electron beam emitter; and
 - at least one target
- comprising a substrate comprising a first selected material;
- said target having a predetermined surface facing the electron beam emitter,
- and having, within the target and adjacent to said predetermined surface,
- a contiguous x-ray generating volume,
- having an orthogonal length and width
- defined in a plane perpendicular to the normal of said predetermined surface,
 - and a depth into the target defined
 - as parallel to the normal of said predetermined surface;
- said x-ray generating volume comprising
- a plurality of discrete structures comprising a second selected x-ray generating material
- that make up a predetermined volume fraction
 - of more than 10% and less than 70% of the x-ray generating volume;
- said source additionally having a predefined set of x-ray propagation cone angles
- having an apex centered at the midpoint of the x-ray generating volume
 - and defined to have an angular range
 - between a minimum angle θ_1 and a maximum angle θ_2
 - relative to an x-ray beam axis defined to have a take-off angle θ_T
 - of less than 105 milliradians;
 - and for which θ_1 is greater than or equal to 2 milliradians,
 - and for which θ_2 is less than or equal to 50 milliradians;
- and, for any ray among a predetermined set of angles
- within the set of x-ray propagation cone angles
 - that overlap the x-ray generating volume,
- the sum of the lengths of the segments of said ray

that overlap x-ray generating material in the x-ray generating volume is less than a predetermined overlap length.

26. The x-ray source of Concept 25, in which
the x-ray generating volume is defined by the overlap
of a predetermined geometric volume
that includes the plurality of discrete structures
with a predetermined electron excitation volume
that will occur when the target is exposed
to a predetermined pattern of electron beam exposure
from the electron beam emitter.
27. The x-ray source of Concepts 25 or 26, in which
the first selected material is selected from the group consisting of:
beryllium, diamond, polycrystalline diamond, diamond-like carbon, graphite, silicon,
boron nitride, silicon carbide, and sapphire.
28. The x-ray source of Concepts 25 through 27, in which
the second selected x-ray generating material is selected from the group consisting of:
aluminum, germanium, titanium, vanadium, chromium, manganese, iron, cobalt,
nickel, copper, gallium, zinc, yttrium, zirconium, molybdenum, niobium, ruthenium,
rhodium, palladium, silver, tin, iridium, tantalum, tungsten, indium, cesium, barium,
germanium, gold, platinum, lead, and combinations and alloys thereof.
29. The x-ray source of Concept 28, in which
an x-ray energy corresponding to the selected second x-ray generating material
is selected,
and said second x-ray generating material has a linear attenuation length μ_L
corresponding to said x-ray energy,
and in which the predetermined overlap length
is greater than or equal to 0.3 times μ_L
and less than or equal to 4 times μ_L .

30. The x-ray source of Concept 29, in which
said predetermined overlap length
is greater than or equal to 1 times μ_l
and less than or equal to 2 times μ_l .

CLAIMS

We claim:

1. A high brightness x-ray source comprising:
 - a vacuum chamber;
 - and, within the vacuum chamber,
 - at least one electron beam emitter; and
 - at least one targetcomprising a substrate comprising a first selected material;
 - said target having a predetermined surface facing the electron beam emitter,
 - and having, within the target and adjacent to said predetermined surface,
 - a contiguous x-ray generating volume
 - having an orthogonal length and width
 - defined in a plane perpendicular to the normal of said predetermined surface,
 - and a depth into the target defined as parallel to the normal of said predetermined surface;
 - said x-ray generating volume comprising:
 - a plurality of discrete structures comprising a second selected x-ray generating material
 - that make up a predetermined volume fraction
 - of more than 10% and less than 70% of the x-ray generating volume;
 - said source additionally having an x-ray beam axis
 - selected to have a take-off angle of less than 6 degrees;
 - and, for any ray oriented parallel to the x-ray beam axis
 - that overlaps with the x-ray generating volume,
 - the sum of the lengths of the segments of said ray
 - that overlap x-ray generating material in the x-ray generating volume
 - is less than a predetermined overlap length.

2. The x-ray source of Claim 1, in which
the first selected material is selected from the group consisting of:
beryllium, diamond, polycrystalline diamond, diamond-like carbon, graphite, silicon,
boron nitride, silicon carbide, and sapphire.
3. The x-ray source of Claim 1, in which
the x-ray generating volume is defined by the overlap
of a predetermined geometric volume
that includes the plurality of discrete structures
with a predetermined electron excitation volume
that will occur when the target is bombarded
with a predetermined pattern of electron beam
from the electron beam emitter.
4. The x-ray source of Claim 3, in which
the predetermined volume fraction of x-ray generating material
is between 30 and 50% of the x-ray generating volume.
5. The x-ray source of Claim 3, in which
the take-off angle is less than 3 degrees.
6. The x-ray source of Claim 3, in which
the length of the x-ray generating volume
that intersects a plane orthogonal to the target surface
and containing the x-ray beam axis
is greater than or equal to 1 micron and less than or equal to 500 microns.
7. The x-ray source of Claim 3, in which
the discrete structures comprising a second selected x-ray generating material
are formed from a powder of the selected x-ray generating material
that has been deposited into a recessed region formed in the substrate.

8. The x-ray source of Claim 3, in which
the discrete structures comprising a second selected x-ray generating material
are embedded into the substrate of first selected material, such that
the x-ray generating volume comprises
both the first selected material
and the second selected x-ray generating material.
9. The x-ray source of Claim 8, in which
the length for any one of the discrete structures
along the x-ray beam axis
is less than or equal to 10 micron.
10. The x-ray source of Claim 8, in which
the separation distance between any two of the discrete structures
is greater than or equal to 0.5 micron and less than or equal to 10 microns.
11. The x-ray source of Claim 3, in which
the predetermined geometric volume is defined as the contiguous volume
both containing the plurality of discrete structures
and having minimal surface area.
12. The x-ray source of Claim 3, in which
the boundary in the length and width dimensions
of the predetermined electron excitation volume
is defined by the half-maximum electron intensity.
13. The x-ray source of Claim 3, in which
the second selected x-ray generating material is selected from the group consisting of:
aluminum, titanium, vanadium, chromium, manganese, iron, cobalt, nickel, copper,
gallium, zinc, yttrium, zirconium, molybdenum, niobium, ruthenium, rhodium,
palladium, silver, tin, iridium, tantalum, tungsten, indium, cesium, barium,
germanium, gold, platinum, lead, and combinations and alloys thereof.

14. The x-ray source of Claim 13, in which
an x-ray energy corresponding to the selected second x-ray generating material
is selected,
and said second x-ray generating material has a linear attenuation length μ_L
corresponding to said x-ray energy,
and in which the predetermined overlap length
is less than or equal to 4 times μ_L .
15. The x-ray source of Claim 14, in which
electrons from the electron beam emitter are selected to have a energy
greater than twice said x-ray energy; and
the depth of the electron exposure volume
is equal to the penetration depth for the electrons of a selected energy
in the first selected material.
16. The x-ray source of Claim 1, in which
the plurality of discrete structures are arranged in a linear array.
17. The x-ray source of Claim 1, additionally comprising
at least one overcoat having a thickness of less than 20 microns
covering at least the discrete structures of the target.
18. The x-ray source of Claim 17, in which
the material of the at least one overcoat is selected from the group consisting of:
beryllium, diamond, polycrystalline diamond, CVD diamond, diamond-like carbon,
graphite, silicon, boron nitride, silicon carbide, and sapphire.
19. The x-ray source of Claim 17, in which
the material of the at least one overcoat is selected from the group consisting of:
graphene, silver, copper, gold, tungsten, aluminum, chromium, tin, and titanium.

20. The x-ray source of Claim 1, additionally comprising:
a mechanism to rotate the target
while the target is being bombarded with electrons from said electron beam emitter.
21. The x-ray source of Claim 20, in which
the target is cylindrically symmetric, and
the substrate of the target is attached to a supporting core.
22. The x-ray source of Claim 21, in which
the supporting core comprises copper.
23. The x-ray source of Claim 21, in which
the substrate has a thickness
greater than or equal to 5 micrometers
and less than or equal to 2 millimeters.
24. The x-ray source of Claim 21, in which
the radius of curvature of the substrate is greater than 20 millimeters.

25. A high brightness x-ray source comprising:
- a vacuum chamber;
 - and, within the vacuum chamber,
 - at least one electron beam emitter; and
 - at least one target
- comprising a substrate comprising a first selected material;
- said target having a predetermined surface facing the electron beam emitter,
- and having, within the target and adjacent to said predetermined surface,
- a contiguous x-ray generating volume,
- having an orthogonal length and width
- defined in a plane perpendicular to the normal of said predetermined surface,
 - and a depth into the target defined
 - as parallel to the normal of said predetermined surface;
- said x-ray generating volume comprising
- a plurality of discrete structures comprising a second selected x-ray generating material
- that make up a predetermined volume fraction
 - of more than 10% and less than 70% of the x-ray generating volume;
- said source additionally having a predefined set of x-ray propagation cone angles
- having an apex centered at the midpoint of the x-ray generating volume
 - and defined to have an angular range
 - between a minimum angle θ_1 and a maximum angle θ_2
 - relative to an x-ray beam axis defined to have a take-off angle θ_f
 - of less than 105 milliradians;
 - and for which θ_1 is greater than or equal to 2 milliradians,
 - and for which θ_2 is less than or equal to 50 milliradians;
- and, for any ray among a predetermined set of angles
- within the set of x-ray propagation cone angles
 - that overlap the x-ray generating volume,
- the sum of the lengths of the segments of said ray

- that overlap x-ray generating material in the x-ray generating volume is less than a predetermined overlap length.
26. The x-ray source of Claim 25, in which
the x-ray generating volume is defined by the overlap
of a predetermined geometric volume
that includes the plurality of discrete structures
with a predetermined electron excitation volume
that will occur when the target is exposed
to a predetermined pattern of electron beam exposure
from the electron beam emitter.
27. The x-ray source of Claim 26, in which
the first selected material is selected from the group consisting of:
beryllium, diamond, polycrystalline diamond, diamond-like carbon, graphite, silicon,
boron nitride, silicon carbide and sapphire.
28. The x-ray source of Claim 26, in which
the second selected x-ray generating material is selected from the group consisting of:
aluminum, germanium, titanium, vanadium, chromium, manganese, iron, cobalt,
nickel, copper, gallium, zinc, yttrium, zirconium, molybdenum, niobium, ruthenium,
rhodium, palladium, silver, tin, iridium, tantalum, tungsten, indium, cesium, barium,
germanium, gold, platinum, lead and combinations and alloys thereof.
29. The x-ray source of Claim 28, in which
an x-ray energy corresponding to the selected second x-ray generating material
is selected,
and said second x-ray generating material has a linear attenuation length μ_L ,
corresponding to said x-ray energy,
and in which the predetermined overlap length
is greater than or equal to 0.3 times μ_L ,
and less than or equal to 4 times μ_L .

30. The x-ray source of Claim 29, in which
said predetermined overlap length
is greater than or equal to 1 times μ_l
and less than or equal to 2 times μ_l .

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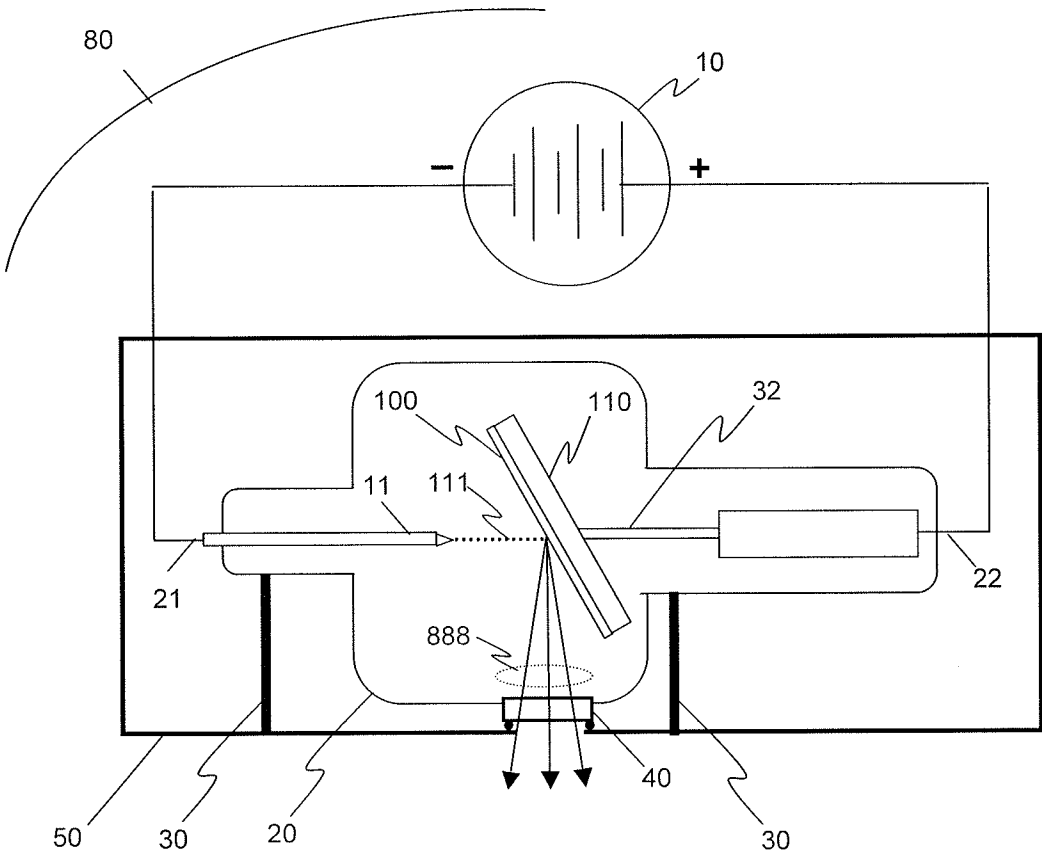


FIG. 1

Prior Art

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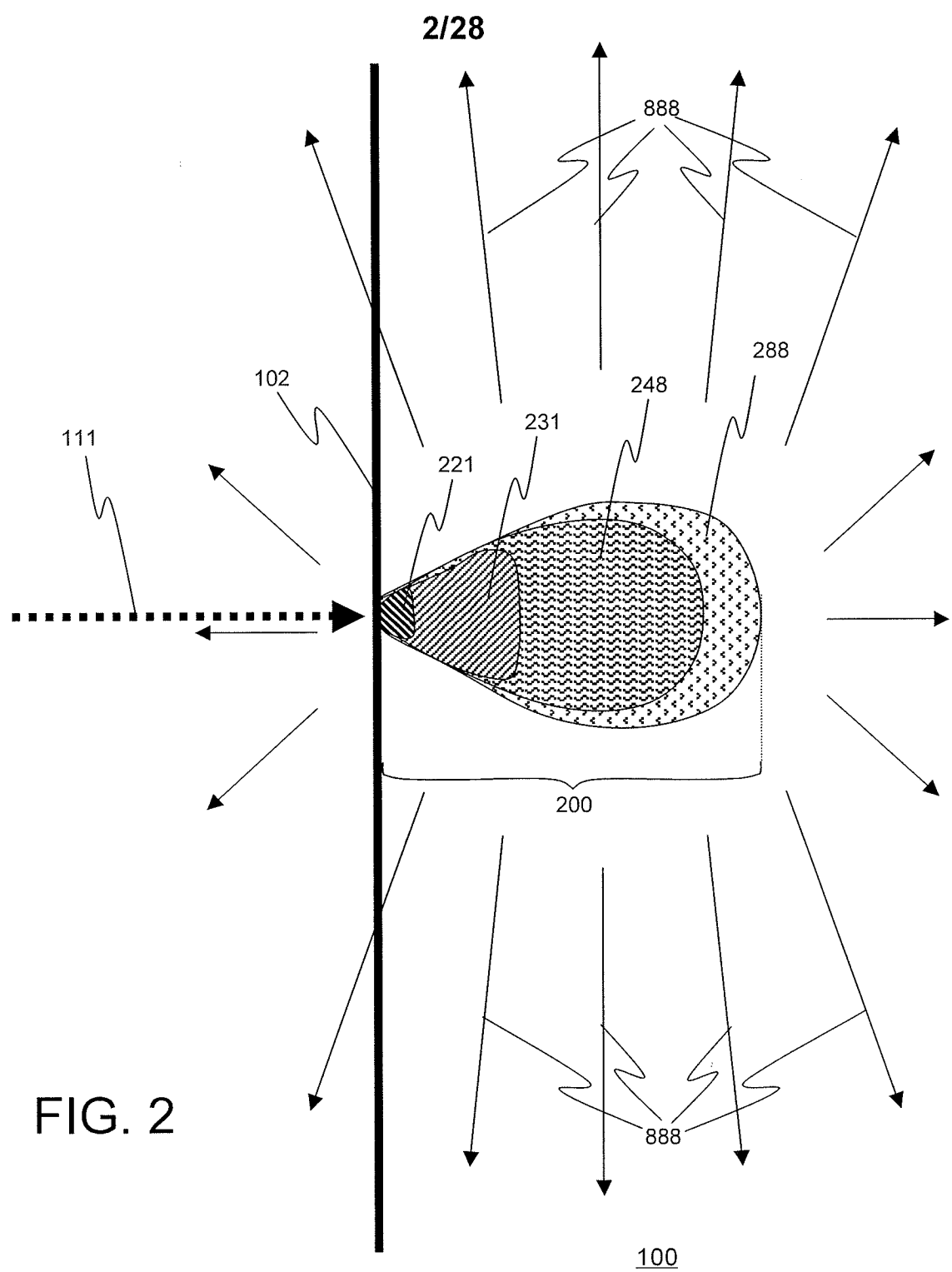


FIG. 2

Prior Art

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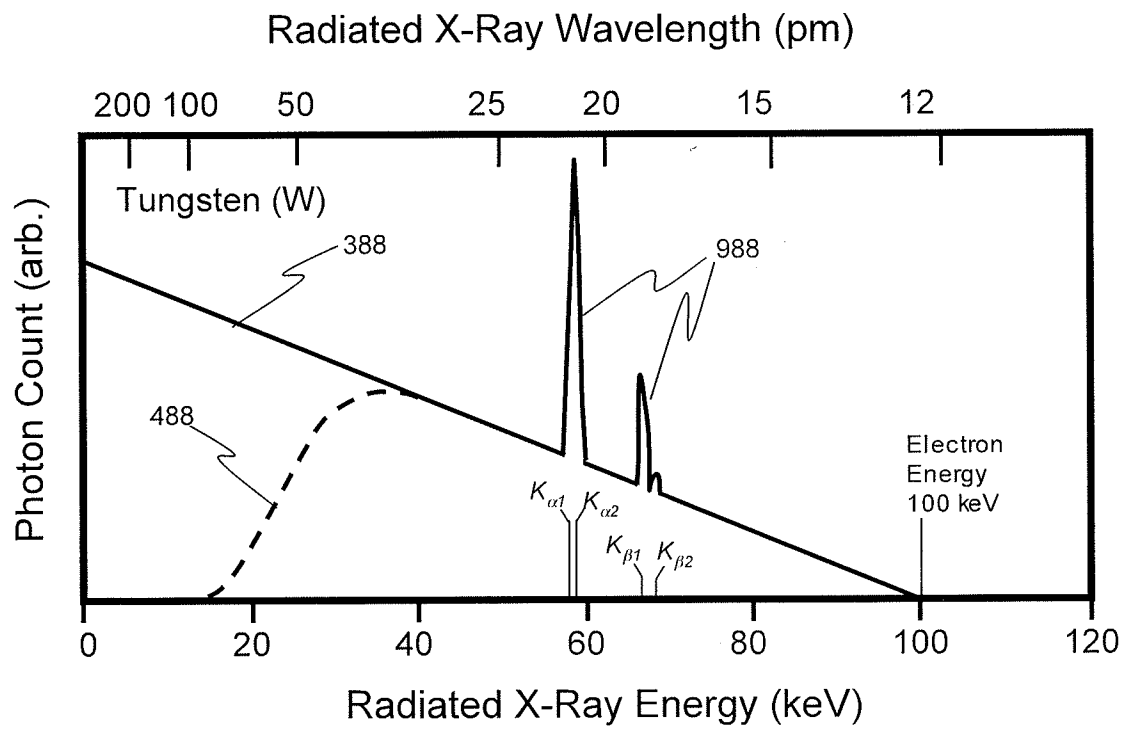


FIG. 3

Prior Art

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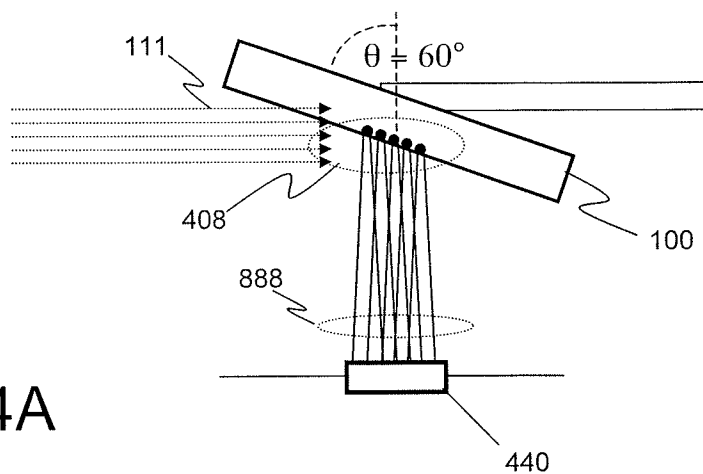


FIG. 4A

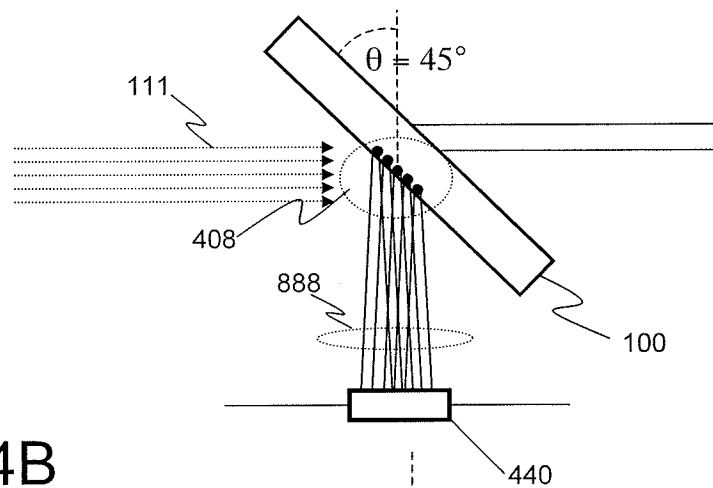


FIG. 4B

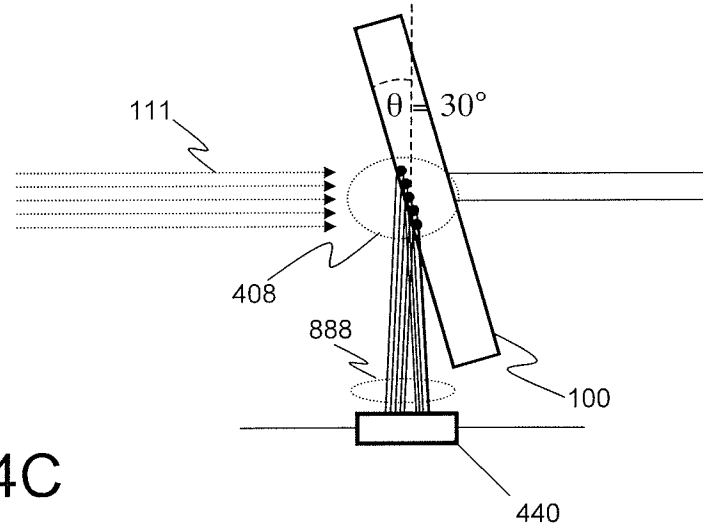


FIG. 4C

Prior Art



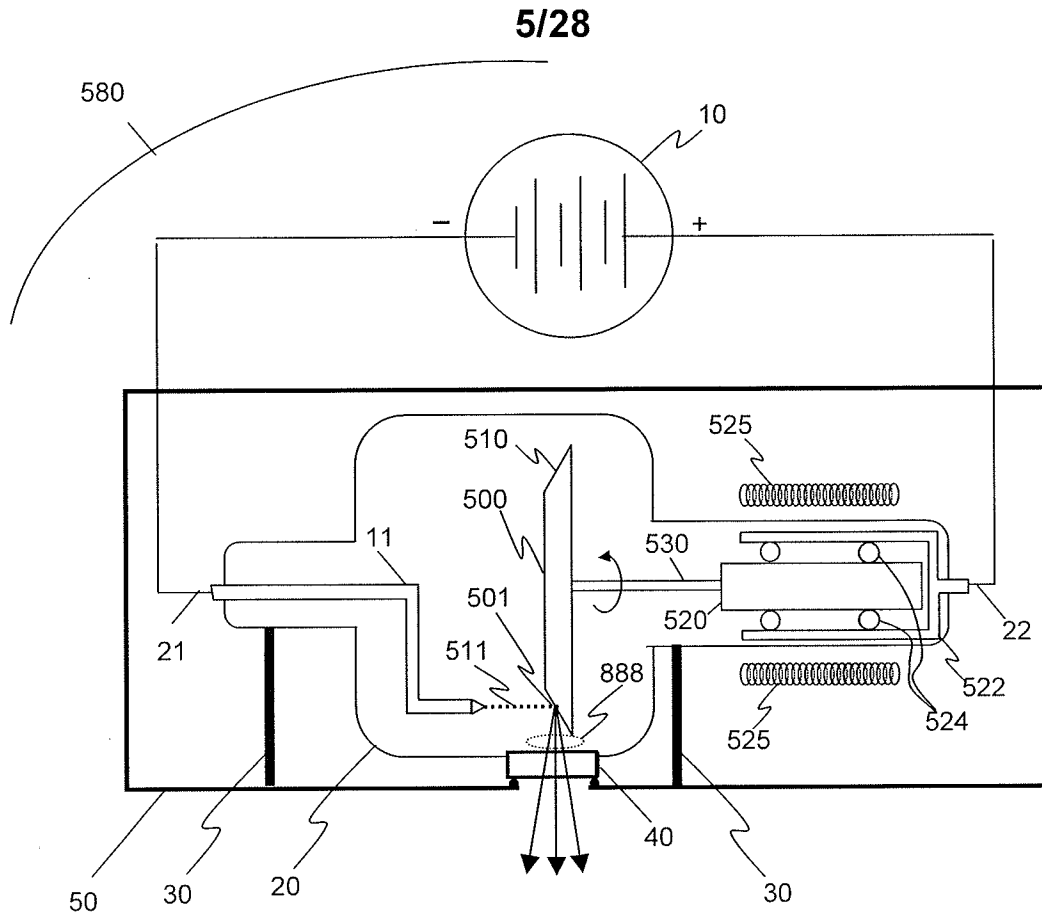


FIG. 5A

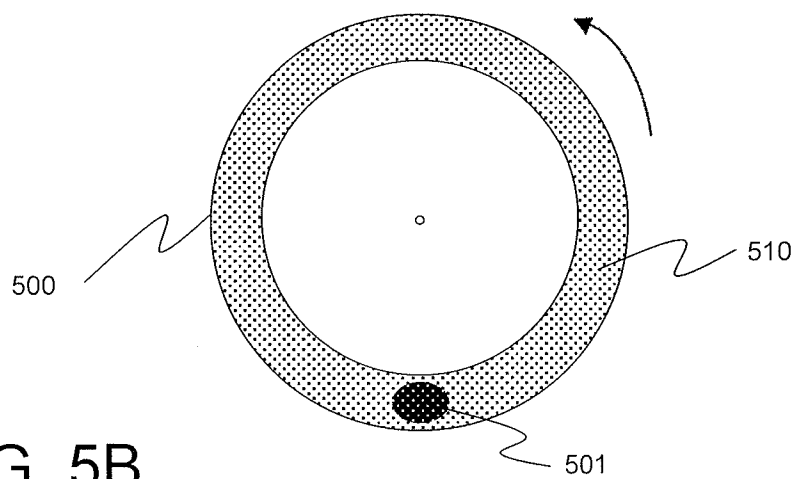


FIG. 5B

Prior Art

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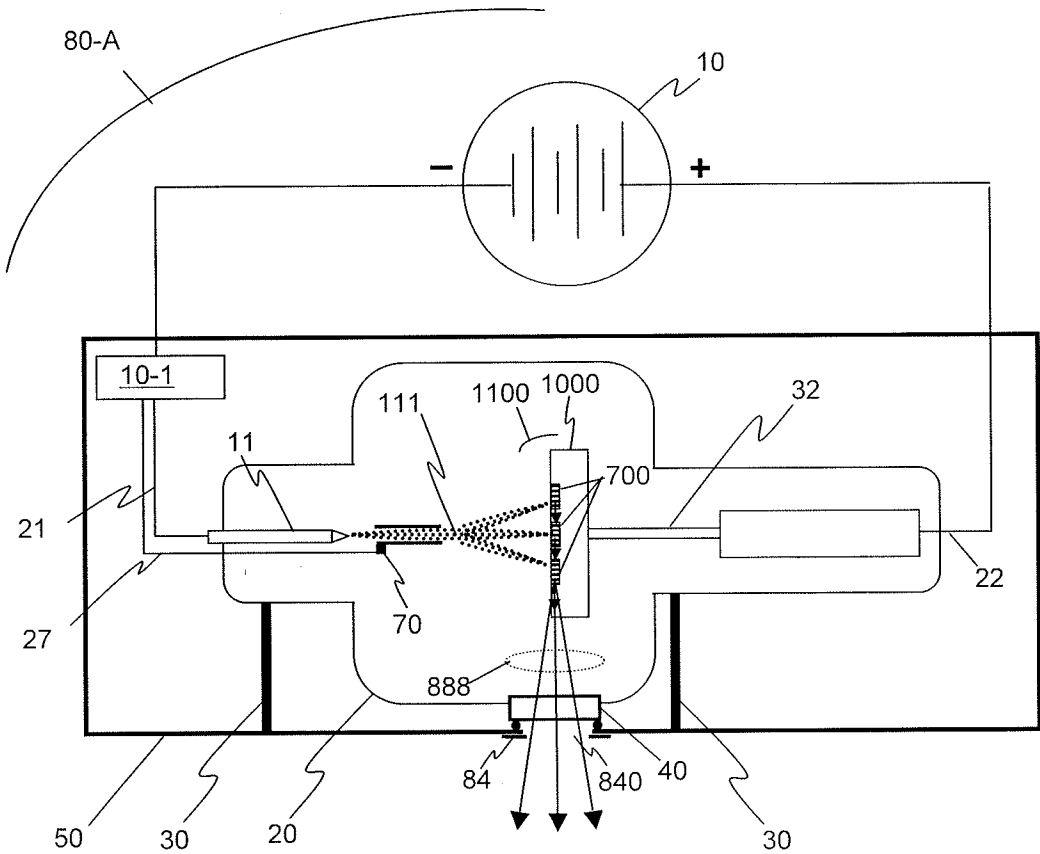


FIG. 6

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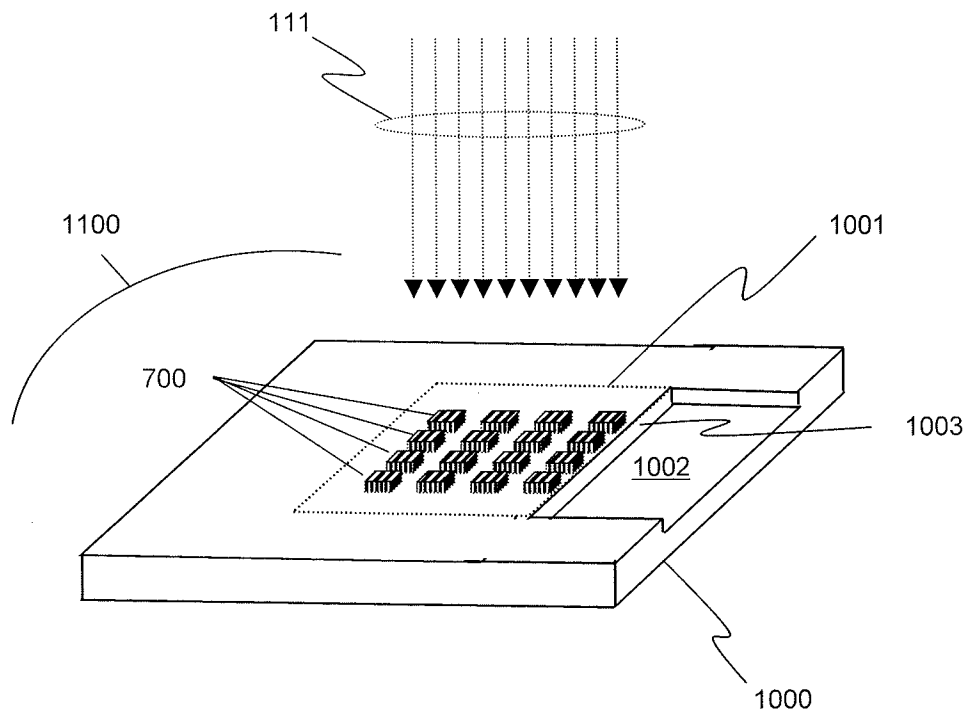


FIG. 7

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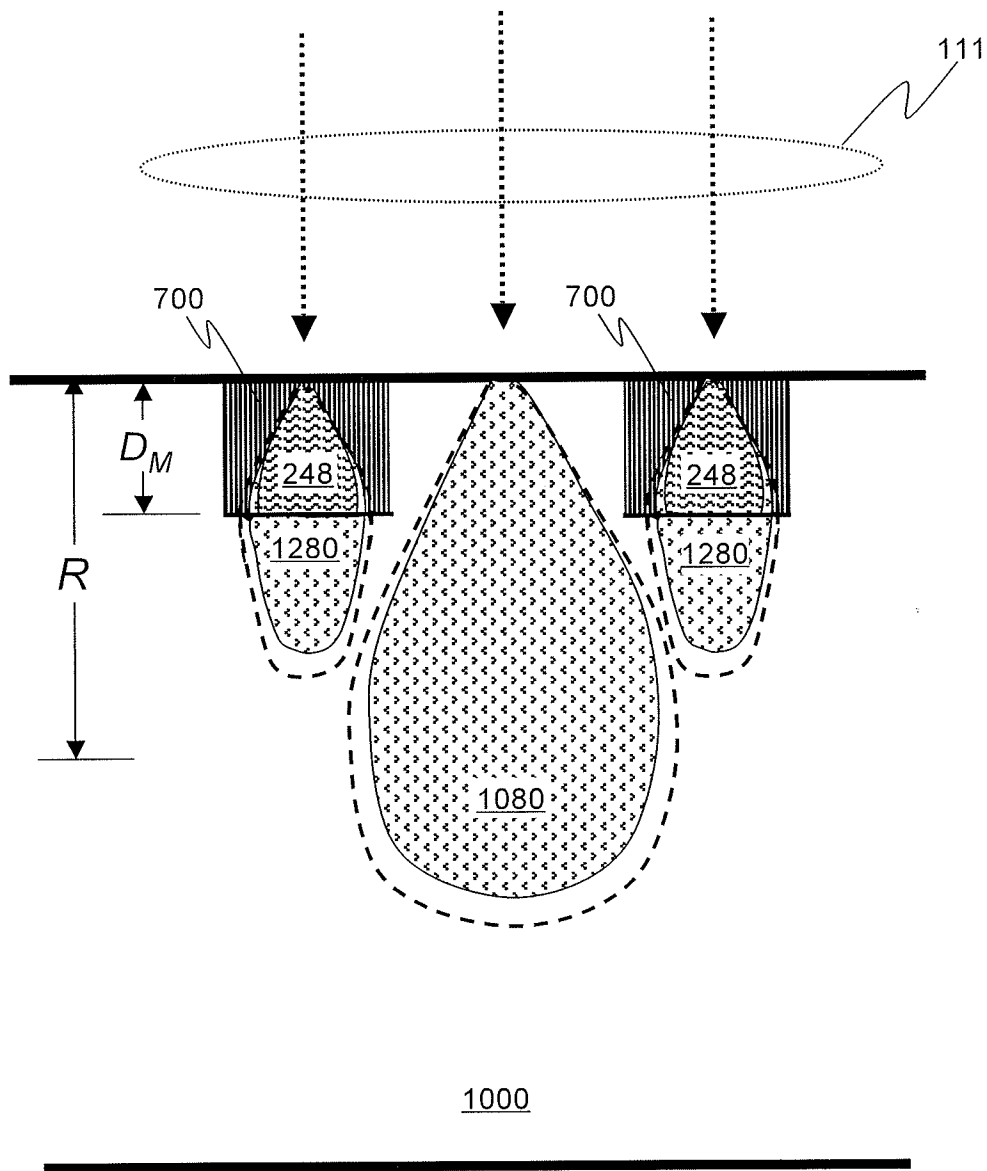


FIG. 8

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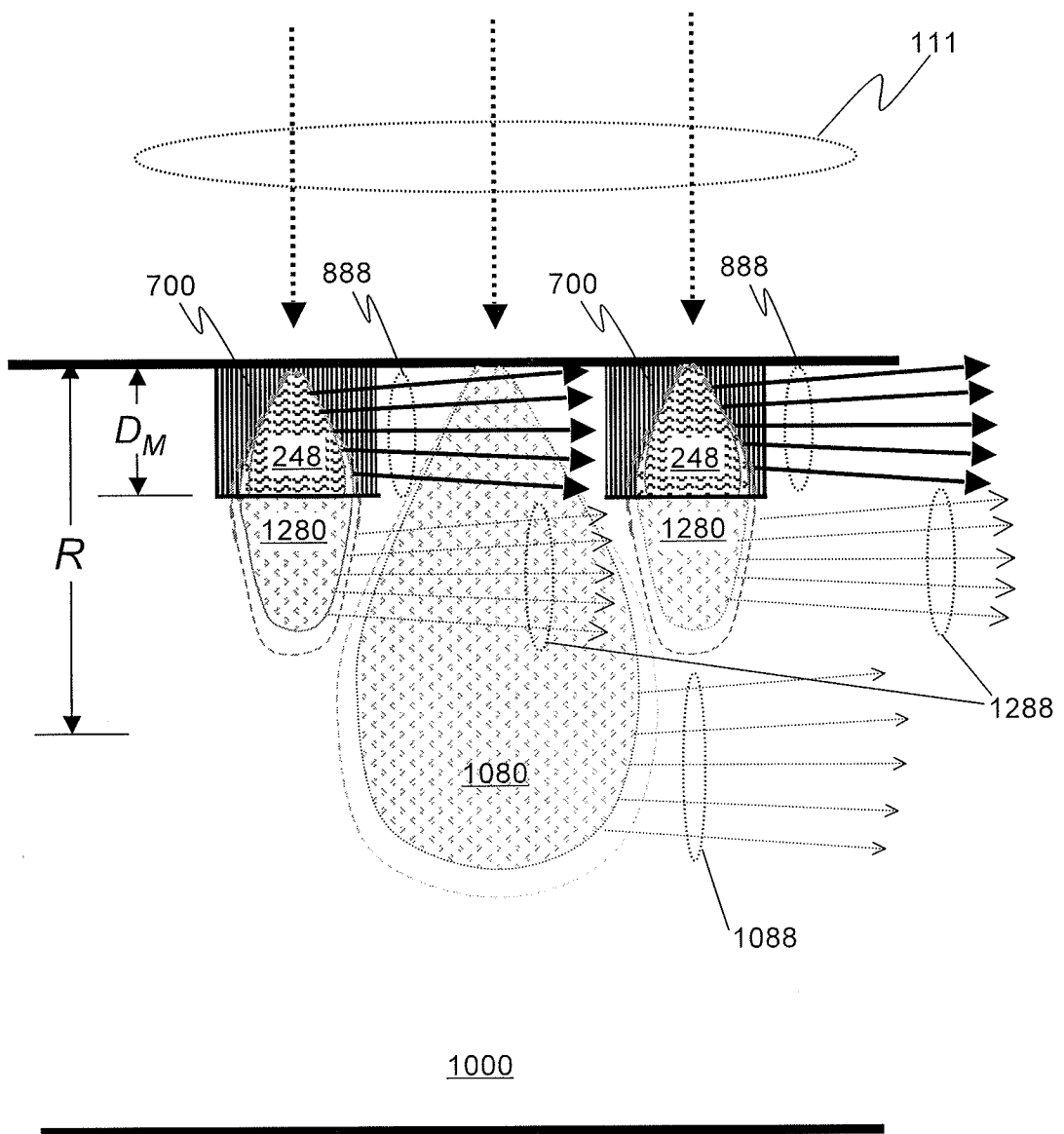


FIG. 9

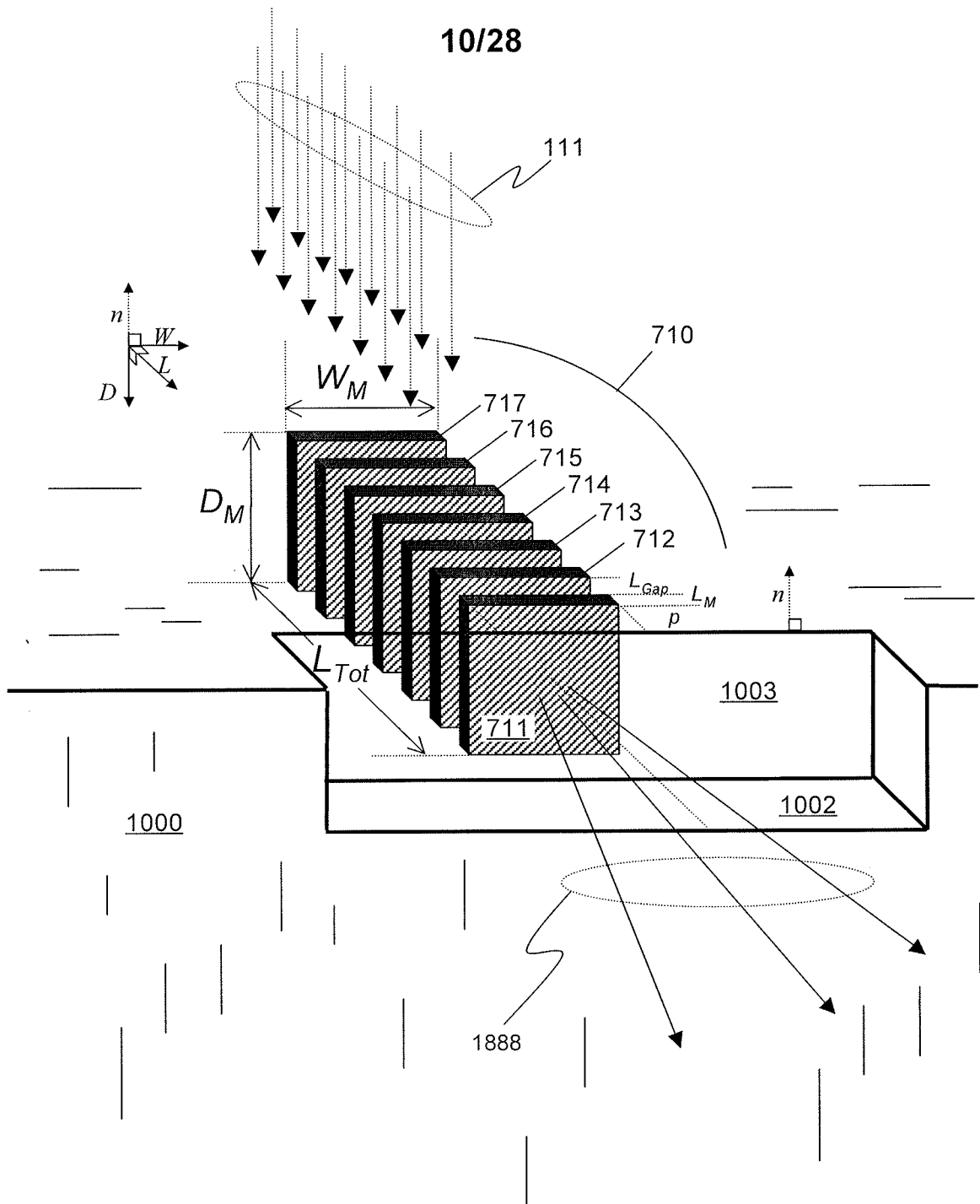


FIG. 10

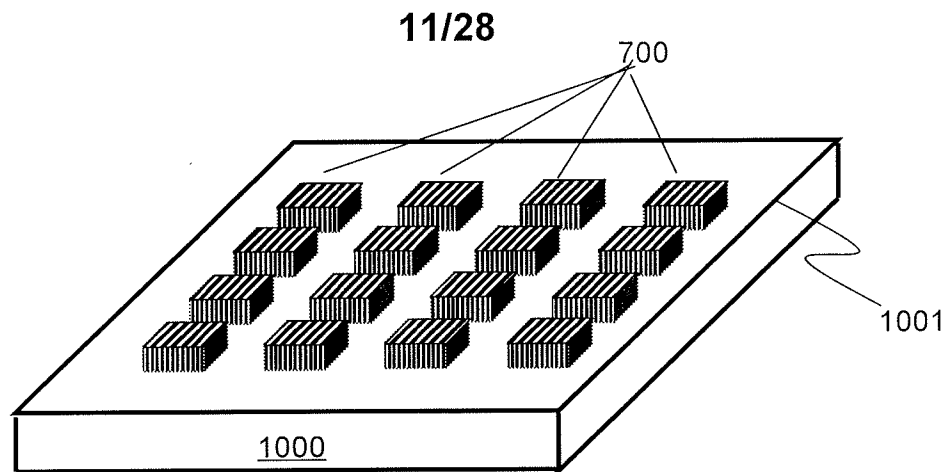


FIG. 11A

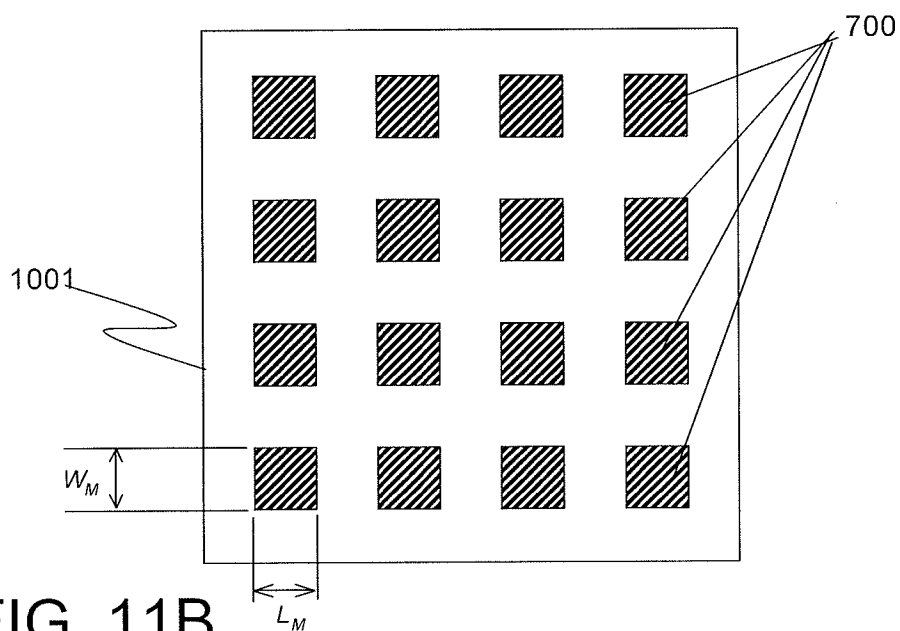


FIG. 11B

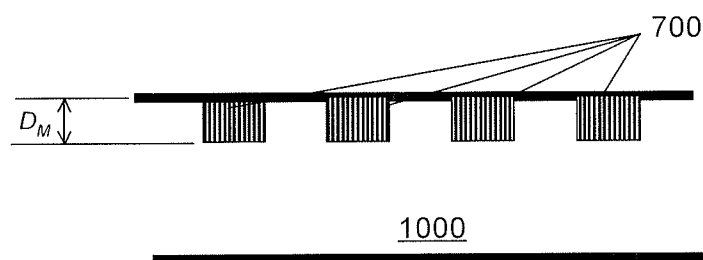


FIG. 11C



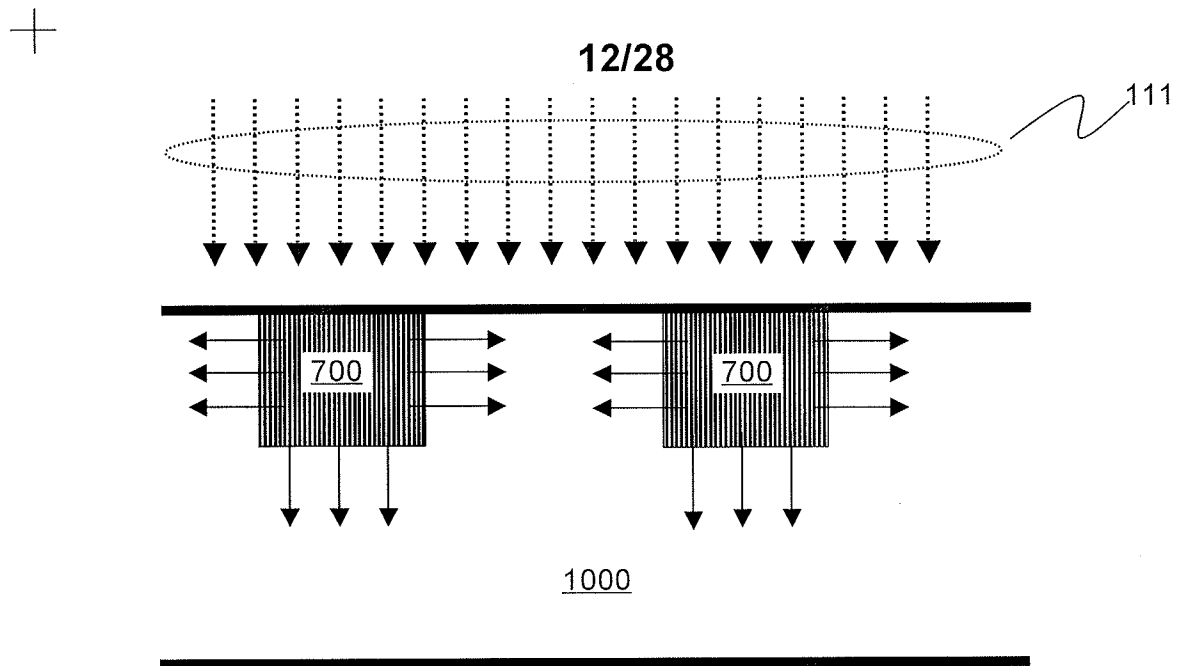


FIG. 12

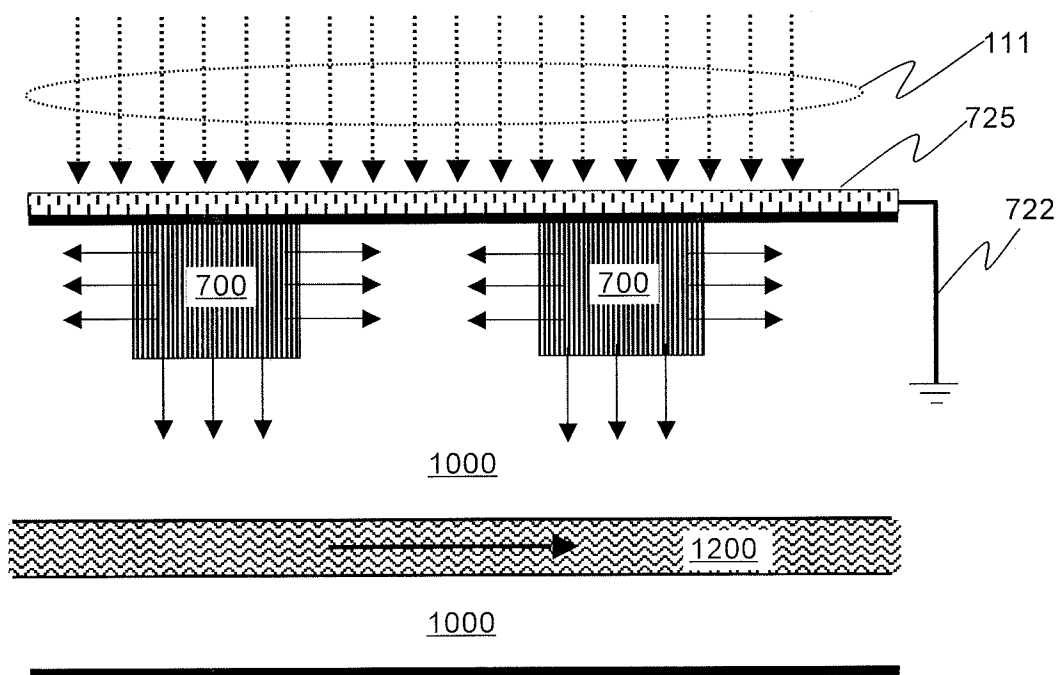


FIG. 13

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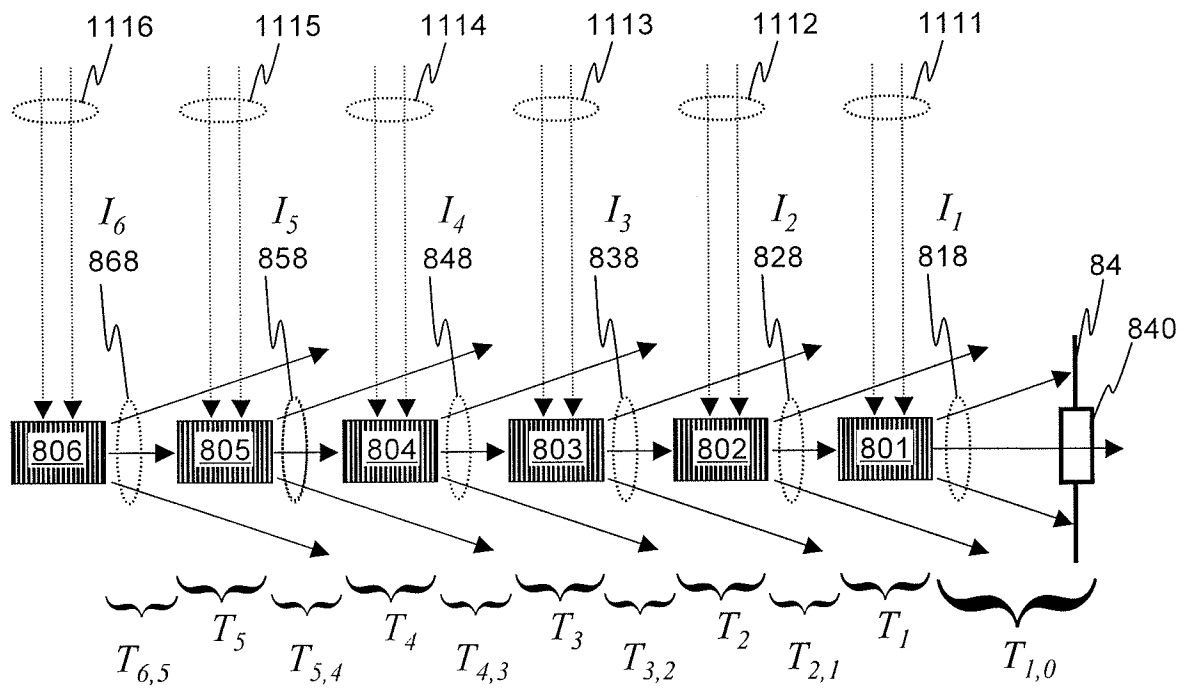


FIG. 14

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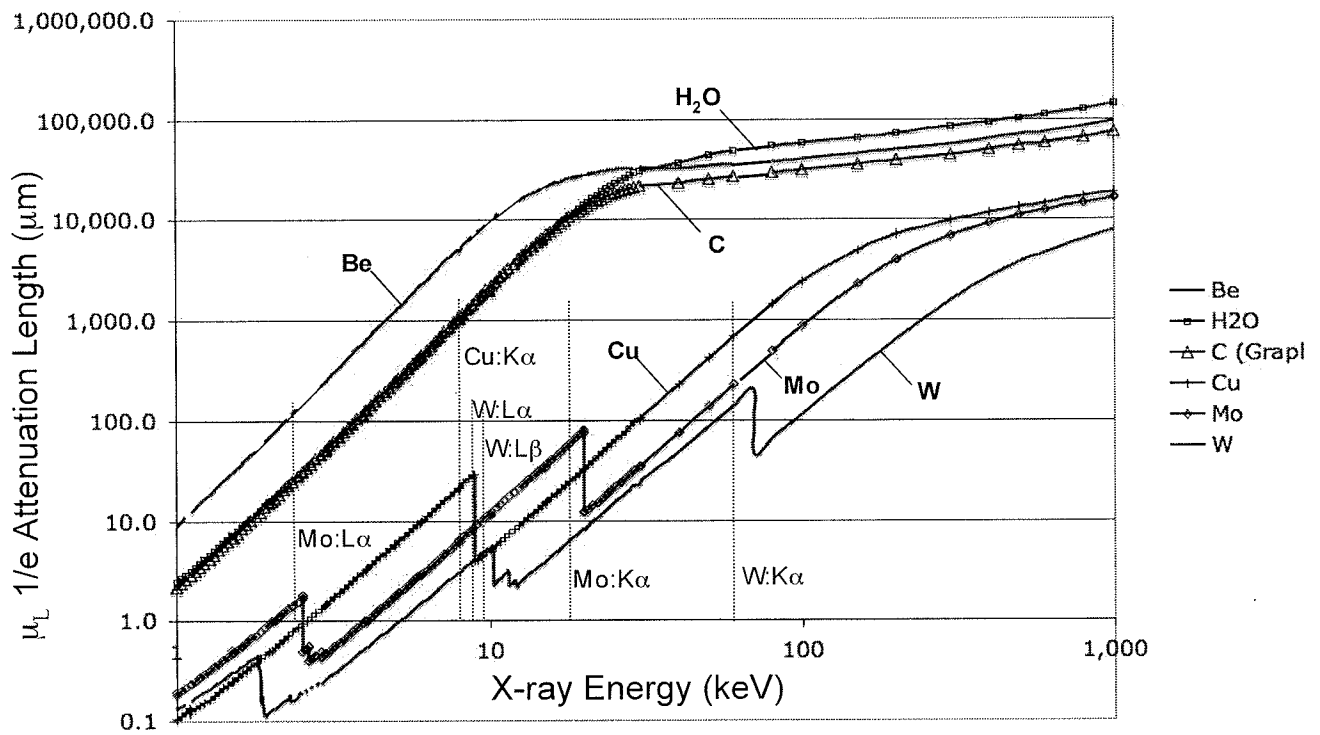


FIG. 15

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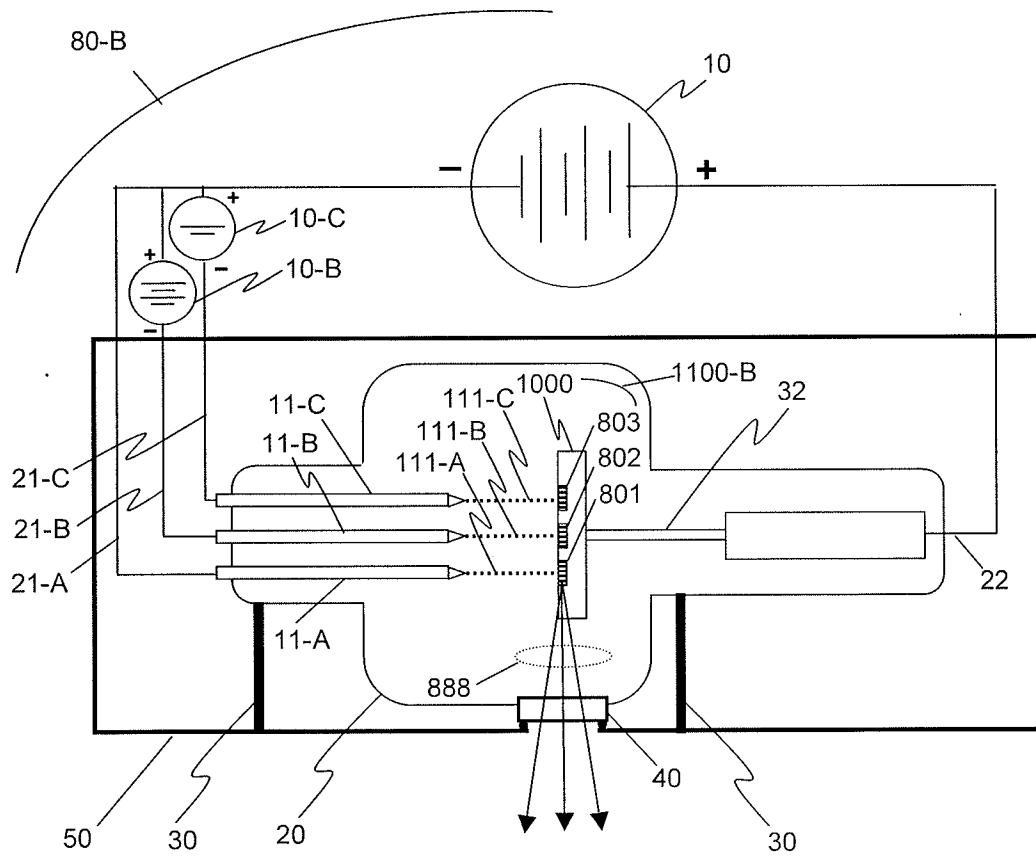


FIG. 16

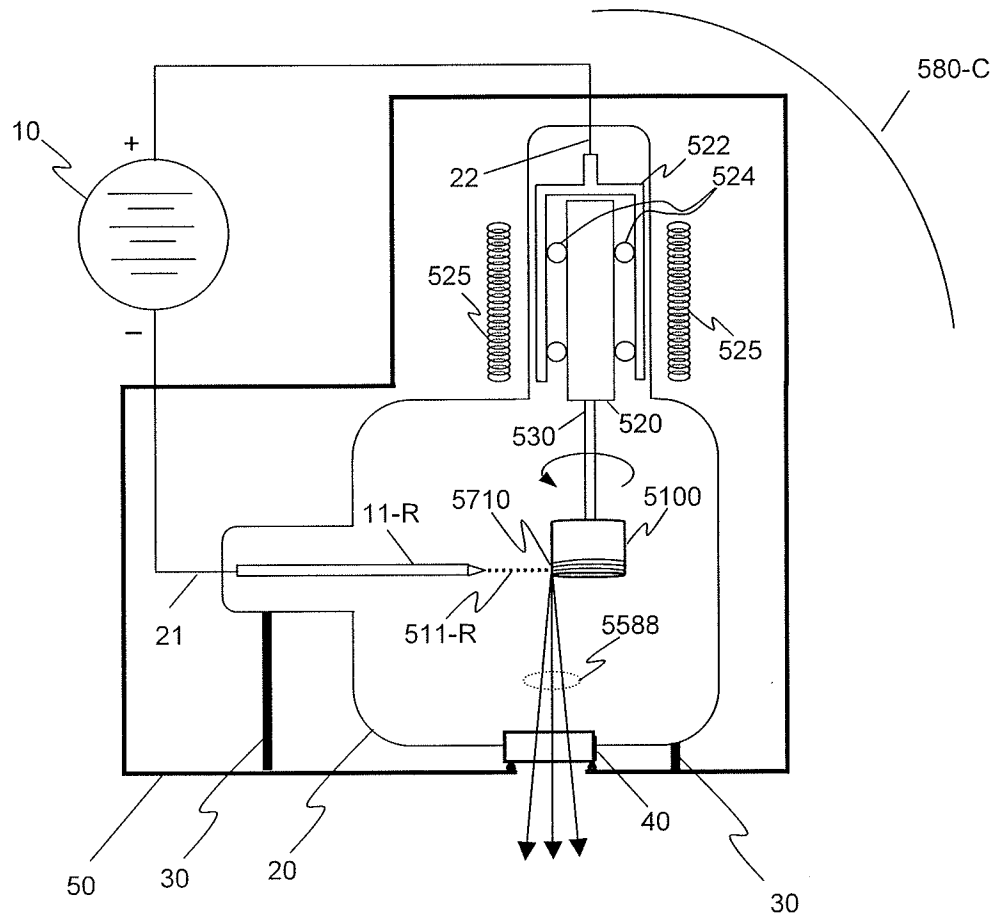


FIG. 17A

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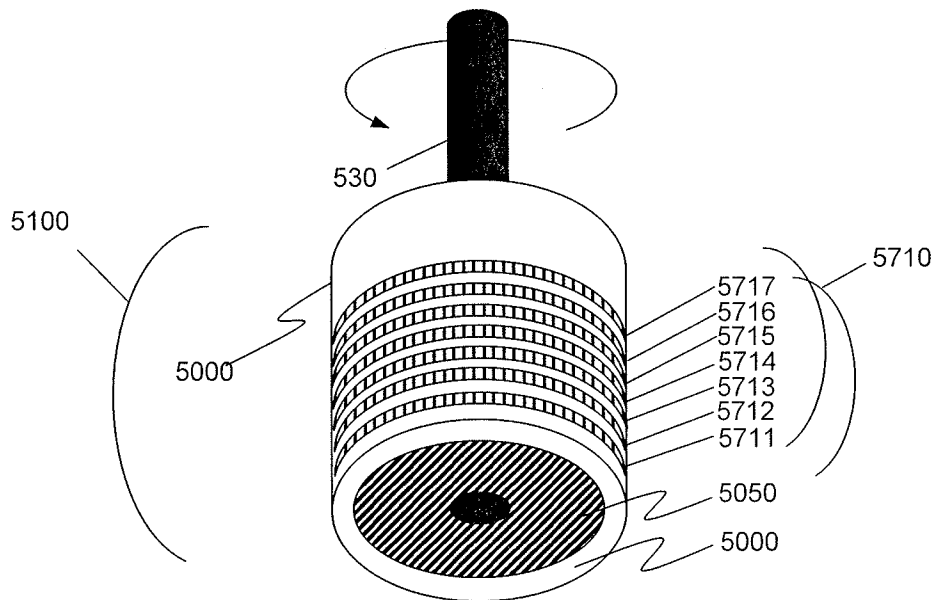


FIG. 17B

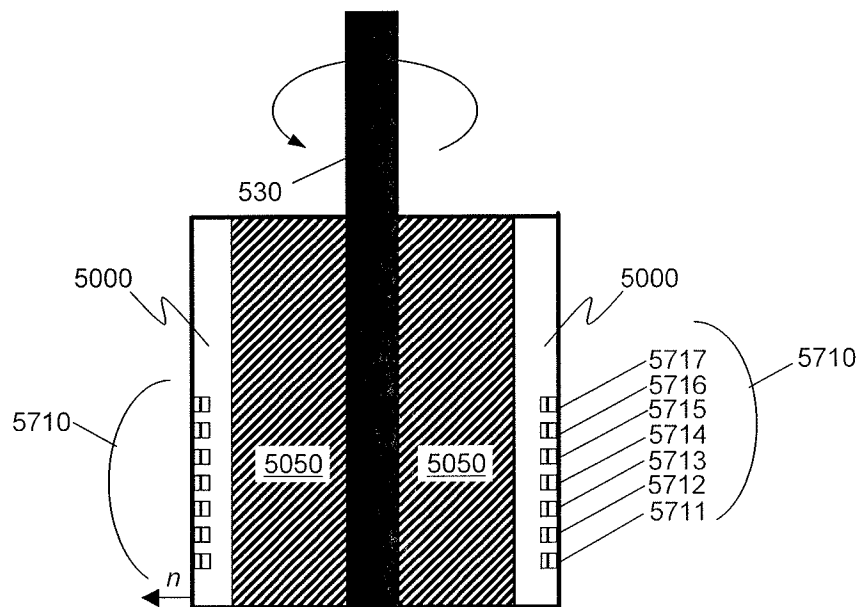


FIG. 17C

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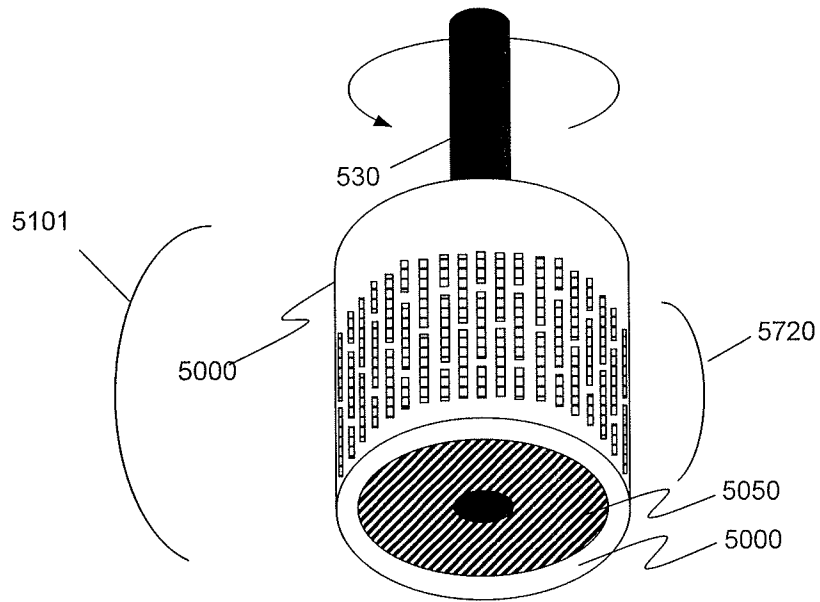


FIG. 18



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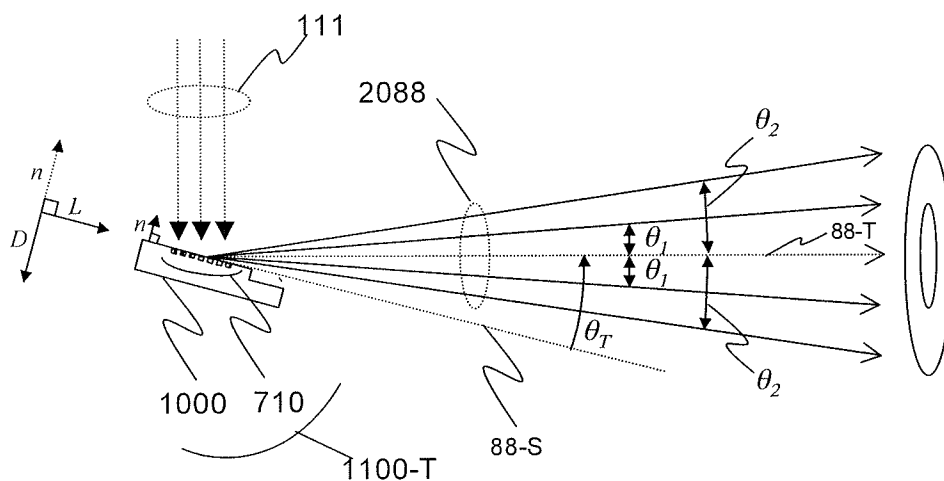


FIG. 19A

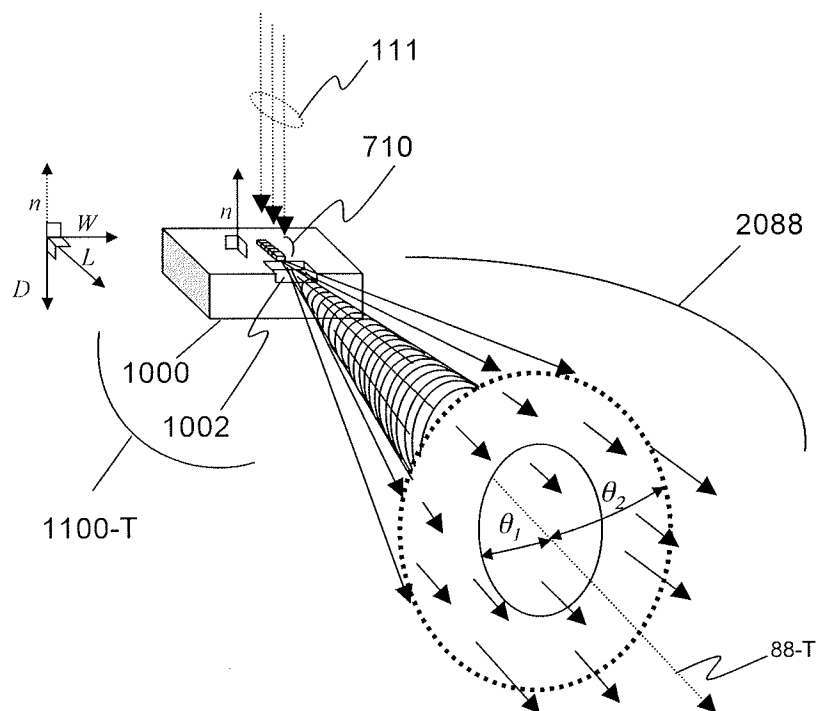


FIG. 19B



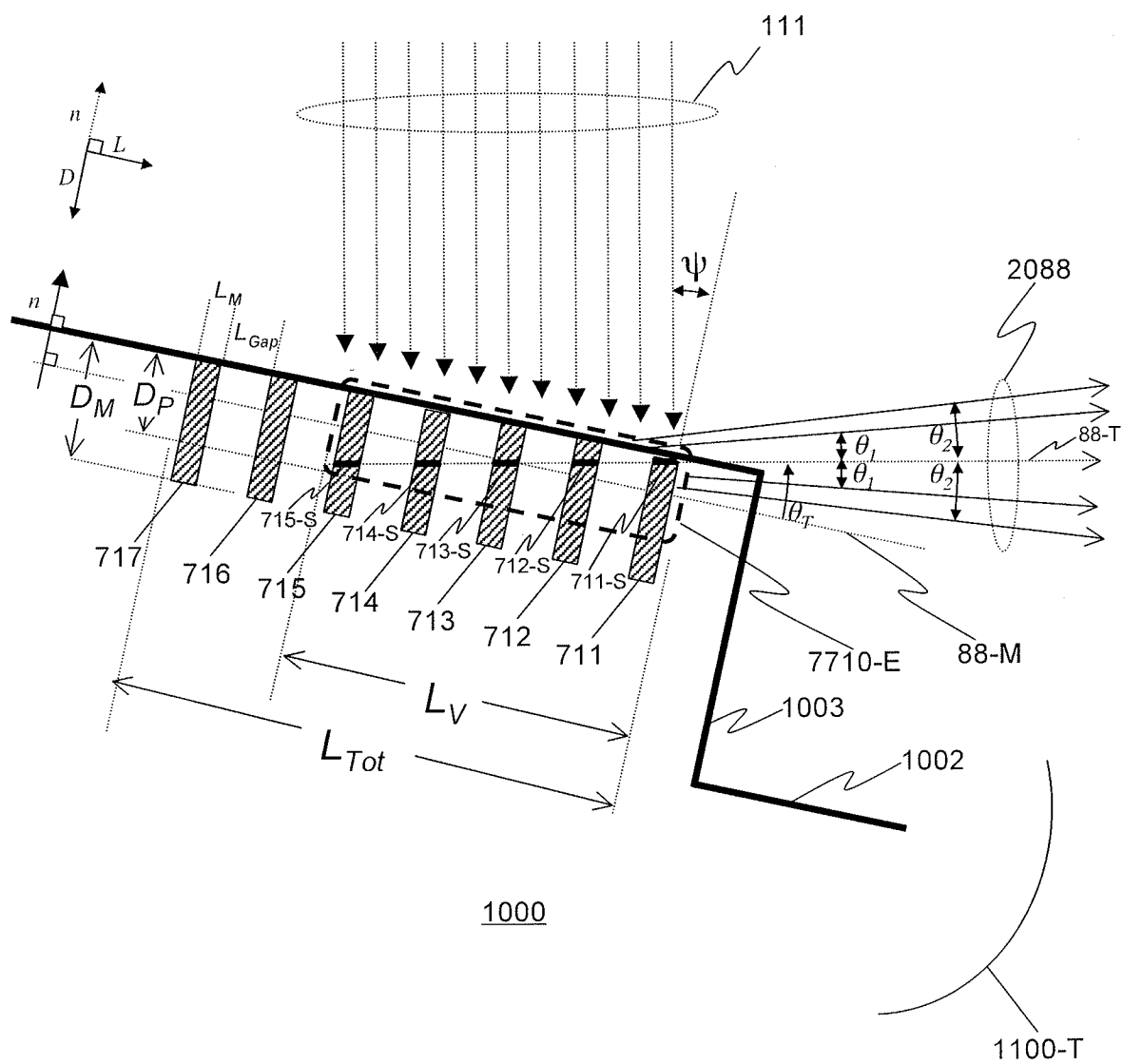


FIG. 19C

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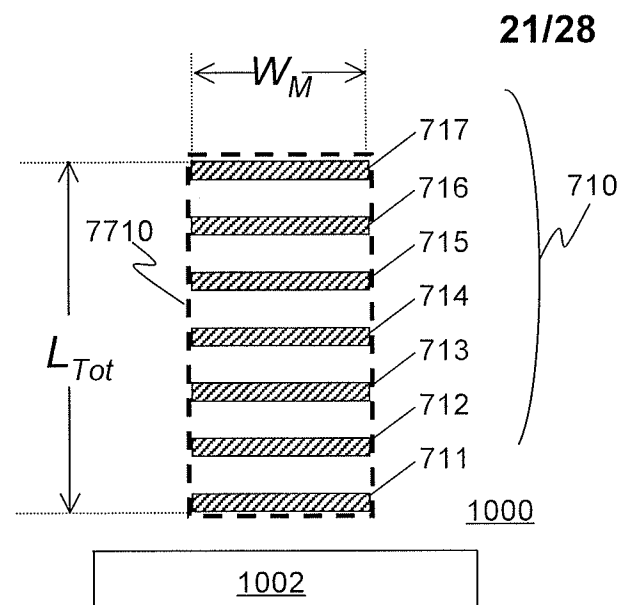


FIG. 20A

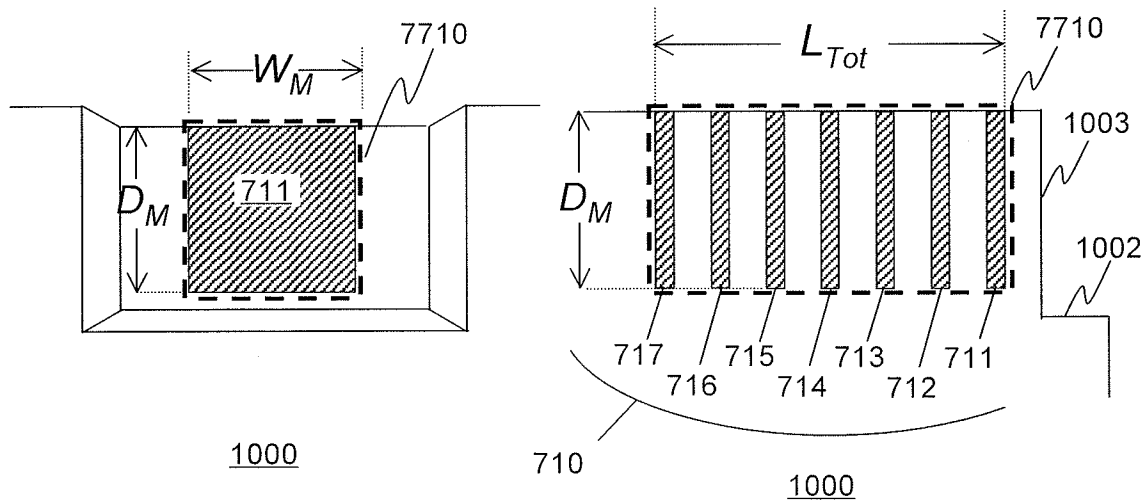


FIG. 20B

FIG. 20C

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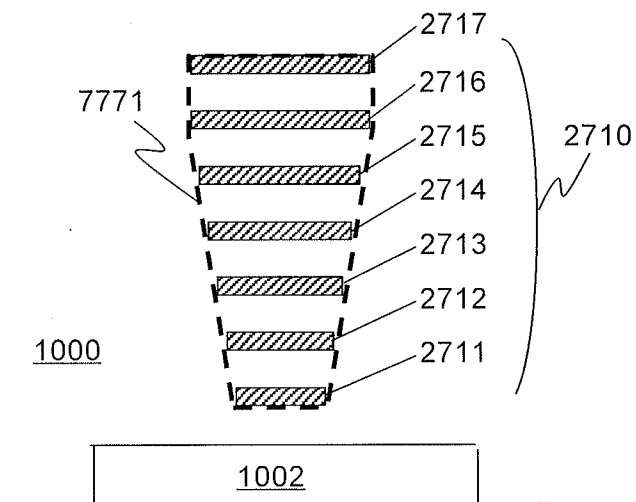


FIG. 21A

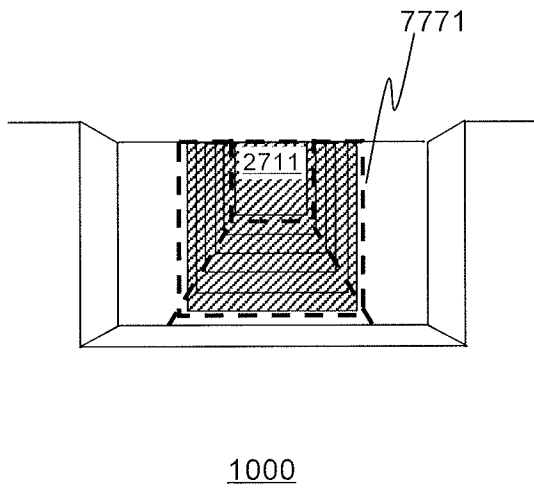


FIG. 21B

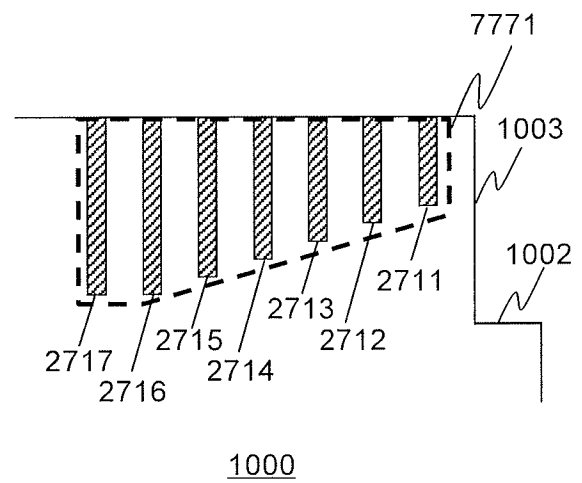


FIG. 21C

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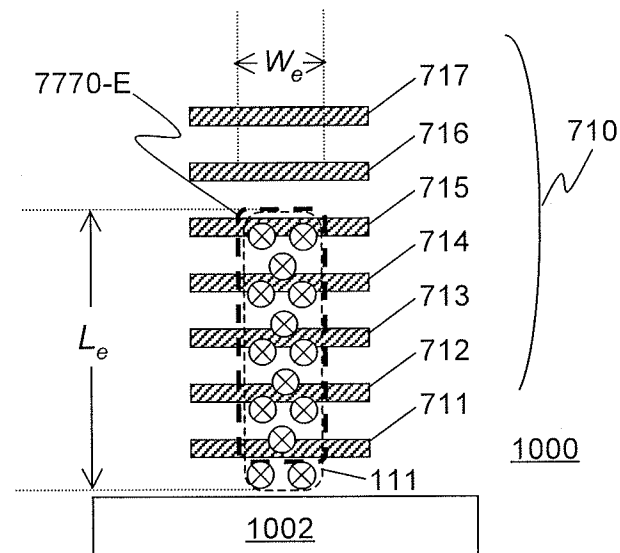


FIG. 22A

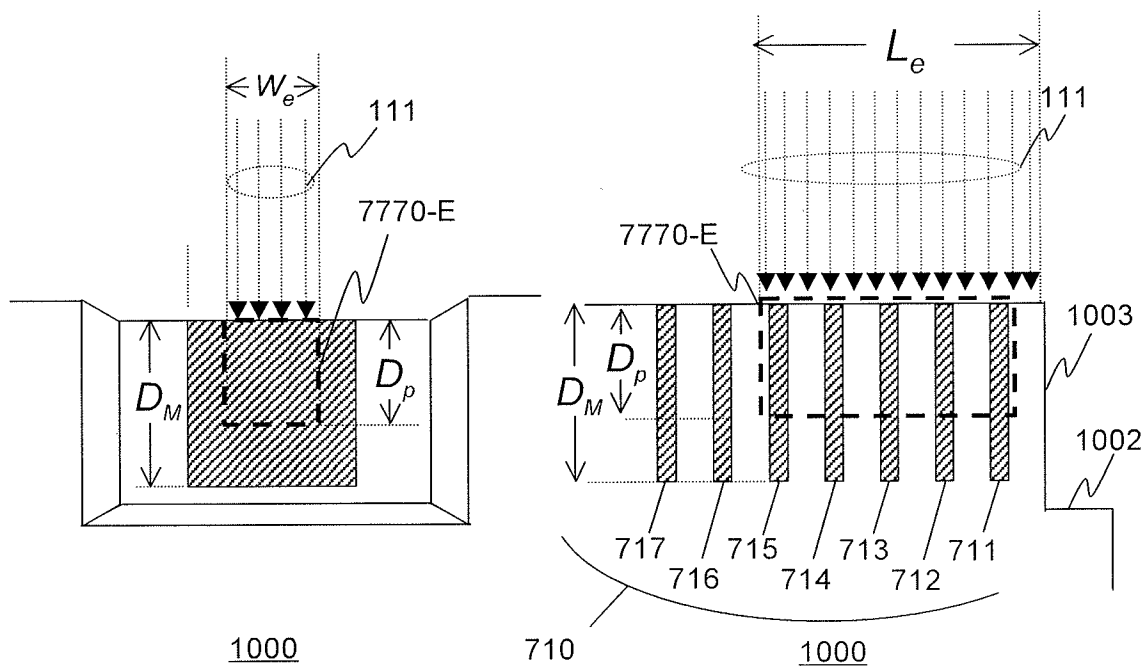


FIG. 22B

FIG. 22C



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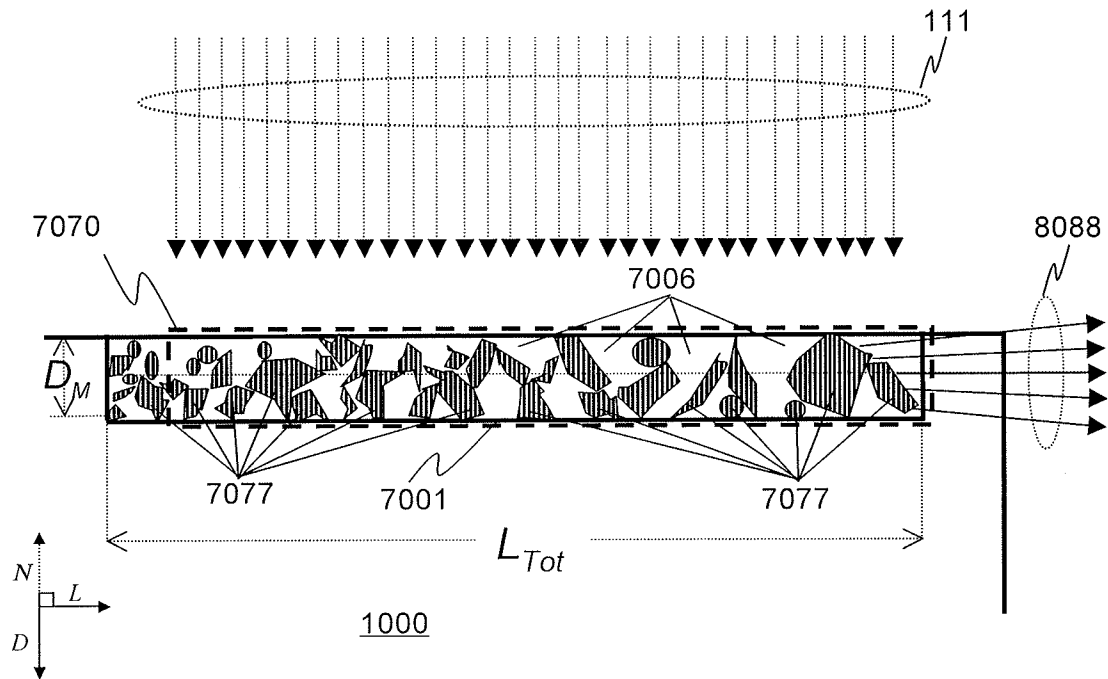


FIG. 23

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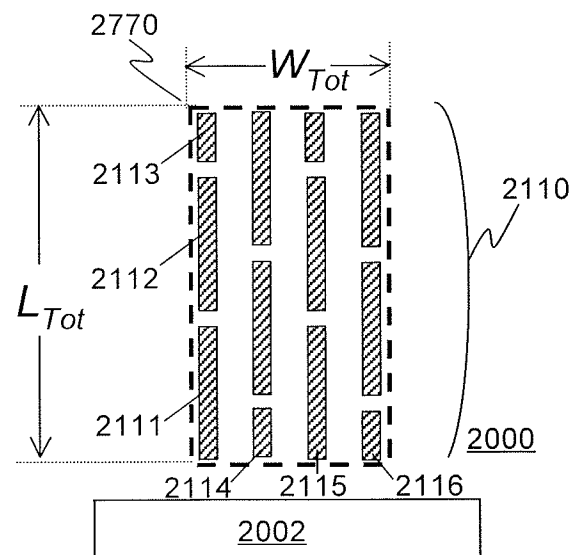


FIG. 24A

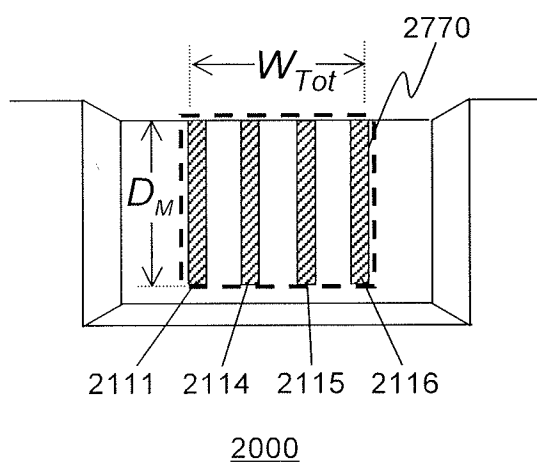


FIG. 24B

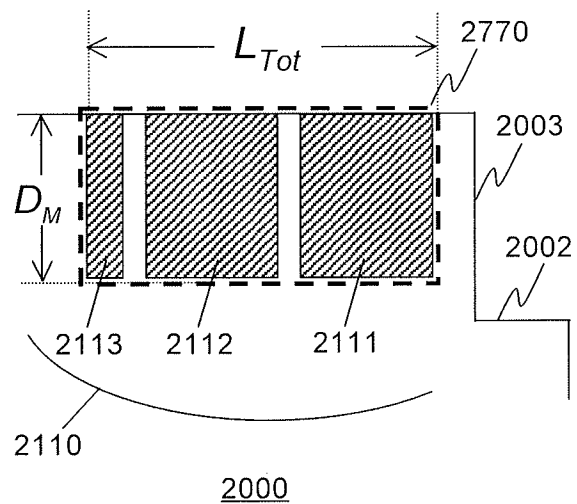


FIG. 24C

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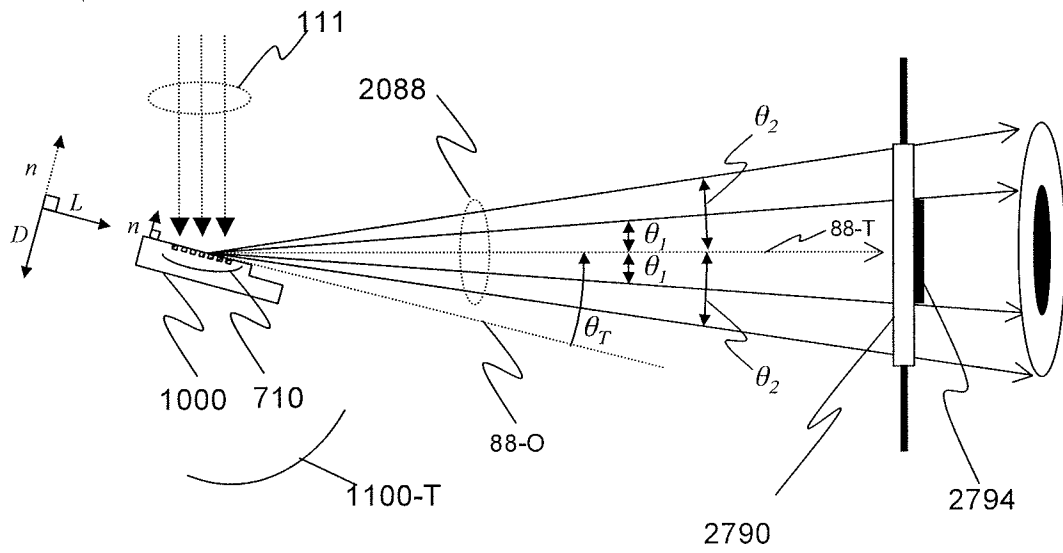


FIG. 25

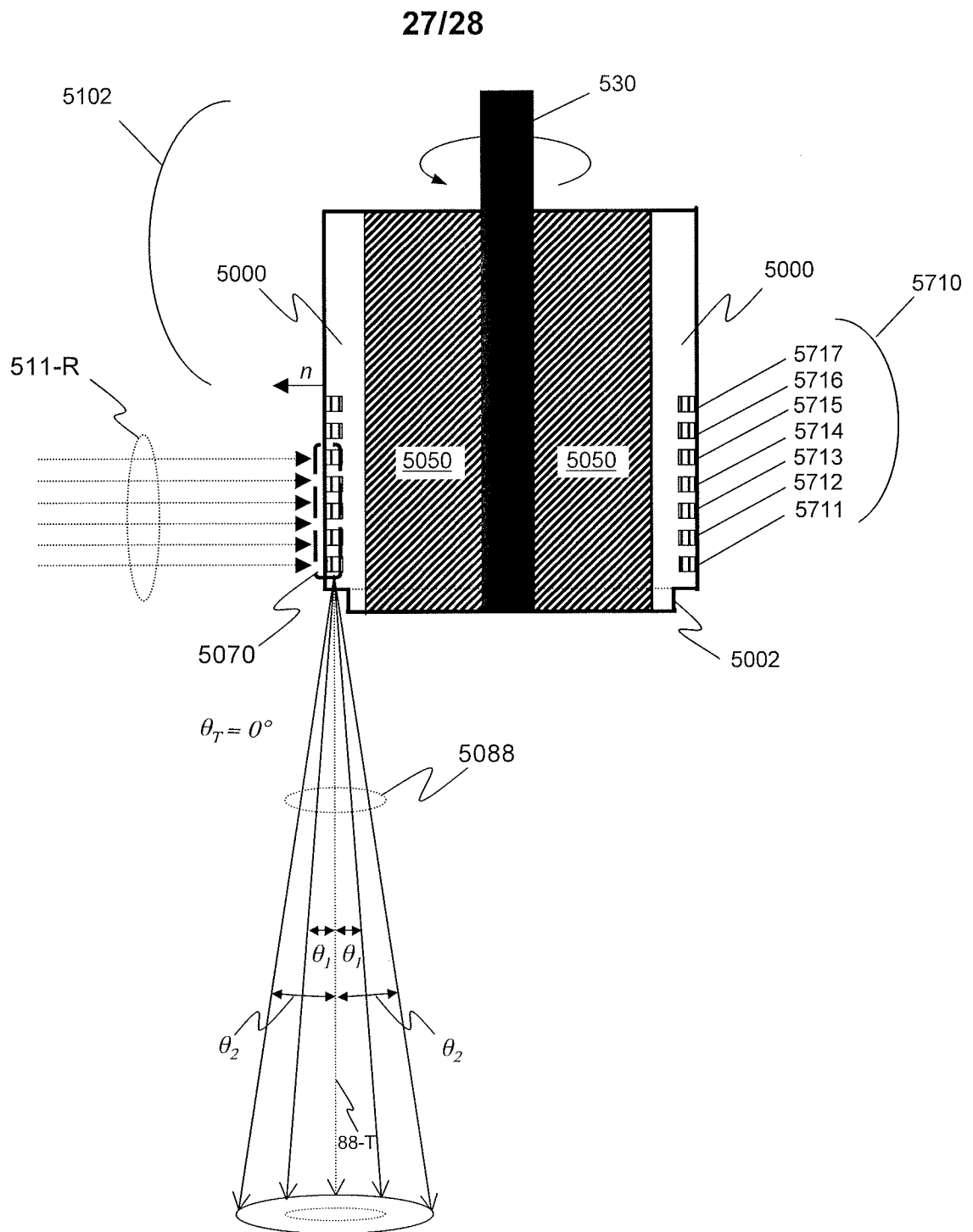


FIG. 26

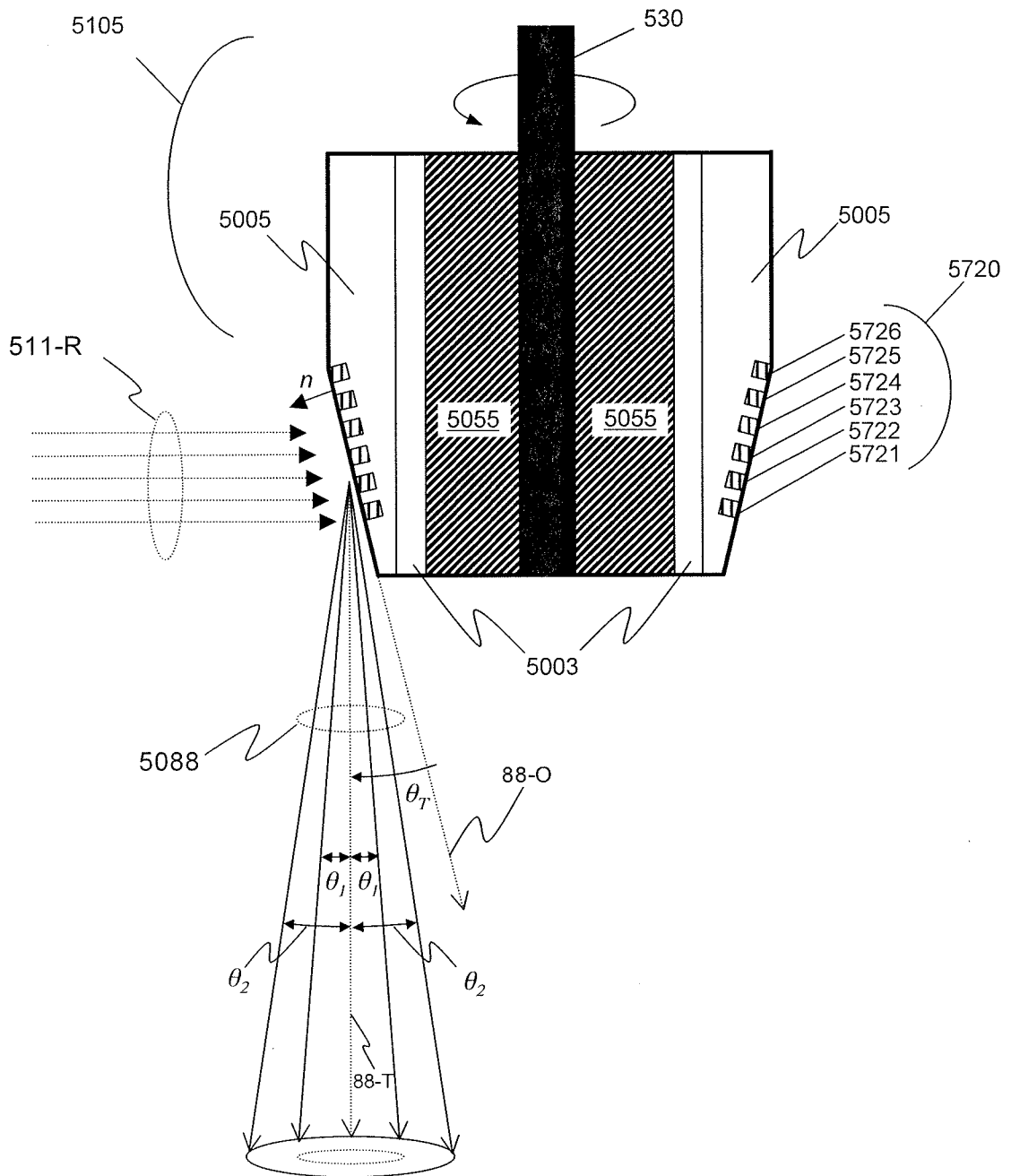


FIG. 27

INTERNATIONAL SEARCH REPORT

International application No.
PCT/US2016/063884**A. CLASSIFICATION OF SUBJECT MATTER****H01J 35/10(2006.01)i, H01J 35/06(2006.01)i, H01J 35/18(2006.01)i**

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

H01J 35/10; H01J 35/08; H05G 1/54; H01J 29/81; A61N 5/10; H01J 35/14; G01N 23/04; H01J 35/18; H01J 35/06

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Korean utility models and applications for utility models

Japanese utility models and applications for utility models

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

eKOMPASS(KIPO internal) & keywords: x-ray source, target, discrete structures, cone angle, brightness, attenuation length

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	US 2015-0110252 A1 (WENBING YUN et al.) 23 April 2015 See paragraphs [0025]-[0026], [0032], [0109]-[0113], [0136]-[0141], [0147] and figures 7, 14-15.	1-30
A	JP 2015-002074 A (CANON INC.) 05 January 2015 See paragraphs [0027]-[0116] and figures 3-6.	1-30
A	US 2013-0223594 A1 (HANS PETER SPRONG et al.) 29 August 2013 See paragraphs [0037]-[0053] and figures 2-4.	1-30
A	US 2011-0038455 A1 (ERIC H. SILVER et al.) 17 February 2011 See paragraphs [0038]-[0055] and figures 9-11.	1-30
A	US 2011-0142204 A1 (YUN ZOU et al.) 16 June 2011 See paragraphs [0044]-[0045] and figures 10-12.	1-30



Further documents are listed in the continuation of Box C.



See patent family annex.

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"&" document member of the same patent family

Date of the actual completion of the international search

09 March 2017 (09.03.2017)

Date of mailing of the international search report

09 March 2017 (09.03.2017)

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